GigaDevice Semiconductor Inc.

GD32E103xx ARM® Cortex[™]-M4 32-bit MCU

Datasheet



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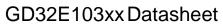




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1. General description

The GD32E103xx device belongs to the connectivity line of GD32 MCU Family. It is a 32-bit general-purpose microcontroller based on the ARM® Cortex™-M4 RISC core with best cost-performance ratio in terms of enhanced processing capacity, reduced power consumption and peripheral set. The Cortex™-M4 core features implements a full set of DSP instructions to address digital signal control markets that demand an efficient, easy-to-use blend of control and signal processing capabilities. It also provides powerful trace technology for enhanced application security and advanced debug support.

The GD32E103xx device incorporates the ARM® Cortex®-M4 32-bit processor core operating at 120 MHz frequency with Flash accesses zero wait states to obtain maximum efficiency. It provides up to 128 KB on-chip Flash memory and 32 KB SRAM memory. An extensive range of enhanced I/Os and peripherals connected to two APB buses. The devices offer up to two 12-bit 3 MSPS ADCs, two 12-bit DACs, up to ten general 16-bit timers, two 16-bit PWM advanced timers, and two 16-bit basic timers, as well as standard and advanced communication interfaces: up to three SPIs, two I2Cs, three USARTs and two UARTs, two I2Ss, an USBFS and two CANs.

The device operates from 1.71 to 3.6 V power supply and available in -40 to +85 °C temperature range. Several power saving modes provide the flexibility for maximum optimization between wakeup latency and power consumption, an especially important consideration in low power applications.

The above features make GD32E103xx devices suitable for a wide range of interconnection and advanced applications, especially in areas such as industrial control, motor drives, consumer and handheld equipment, human machine interface, security and alarm systems, POS, automotive navigation, IoT and so on.





2. Device overview

2.1. Device information

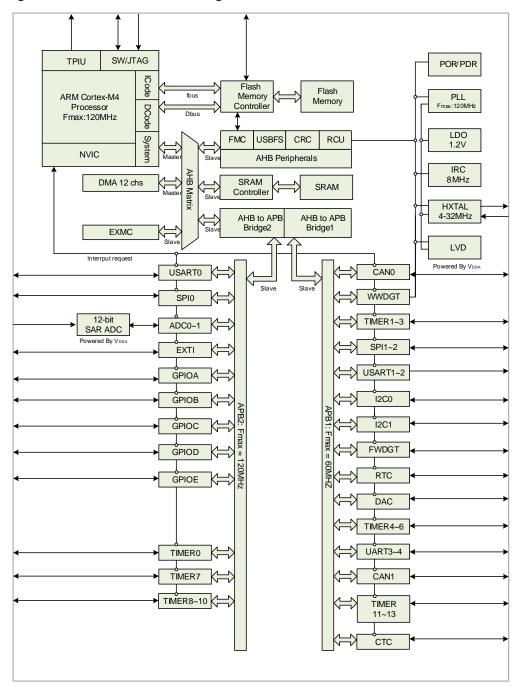
Table 2-1. GD32E103xx devices features and peripheral list

Part Number Flash (KB)		GD32E103xx							
		Т8	ТВ	C8	СВ	R8	RB	V8	VB
		64	128	64	128	64	128	64	128
	SRAM (KB)	20	32	20	32	20	32	20	32
	General timer(16-	4	4	10	10	10	10	10	10
	bit)	(1-4)	(1-4)	(1-4,8-13)	(1-4,8-13)	(1-4,8-13)	(1-4,8-13)	(1-4,8-13)	(1-4,8-13)
	Advanced	1	1	1	1	2	2	2	2
' 0	timer(16-bit)	(0)	(0)	(0)	(0)	(0,7)	(0,7)	(0,7)	(0,7)
Timers	SysTick	1	1	1	1	1	1	1	1
Ē	Basic timer(16-bit)	2	2	2	2	2	2	2	2
	Basic timer (10-bit)	(5,6)	(5,6)	(5,6)	(5,6)	(5,6)	(5,6)	(5,6)	(5,6)
	Watchdog	2	2	2	2	2	2	2	2
	RTC	1	1	1	1	1	1	1	1
	LICART	2	2	3	3	3	3	3	3
	USART	(0-1)	(0-1)	(0-2)	(0-2)	(0-2)	(0-2)	(0-2)	(0-2)
	UART	0	0	0	0	2	2	2	2
Æ						(3-4)	(3-4)	(3-4)	(3-4)
Connectivity	I2C	1	1	2	2	2	2	2	2
Juec	-	(0)	(0)	(0-1)	(0-1)	(0-1)	(0-1)	(0-1)	(0-1)
CO	SPI/I2S	1/0	1/0	3/2	3/2	3/2	3/2	3/2	3/2
		(0/-)	(0/-)	(0-2)/(1-2)	(0-2)/(1-2)	(0-2)/(1-2)	(0-2)/(1-2)	(0-2)/(1-2)	(0-2)/(1-2)
	CAN	2xFD	2xFD	2xFD	2xFD	2xFD	2xFD	2xFD	2xFD
	USBFS	1	1	1	1	1	1	1	1
	GPIO	26	26	37	37	51	51	80	80
EXMC		0	0	0	0	0	0	1	1
	EXTI	16	16	16	16	16	16	16	16
ပ	Units	2	2	2	2	2	2	2	2
ADC	Channels	10	10	10	10	16	16	16	16
	DAC	2	2	2	2	2	2	2	2
	Package	QFI	N36	LQF	- -P48	LQF	P64	LQFF	P100



2.2. Block diagram

Figure 2-1.GD32E103xx block diagram





2.3. Pinouts and pin assignment

Figure 2-2. GD32E103Vx LQFP100 pinouts

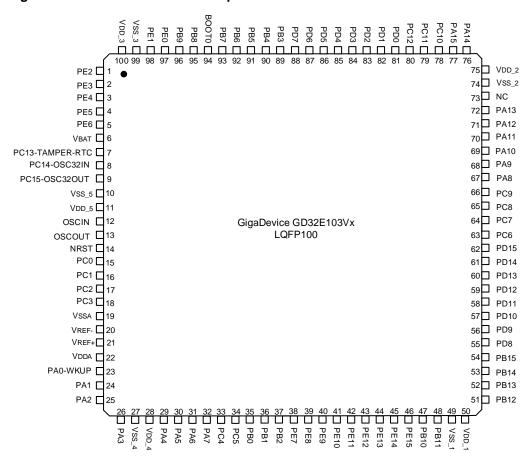




Figure 2-3. GD32E103Rx LQFP64 pinouts

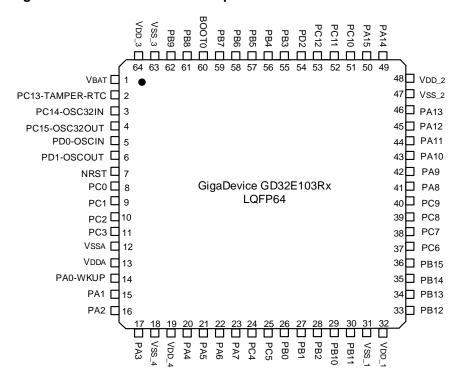


Figure 2-4. GD32E103Cx LQFP48 pinouts

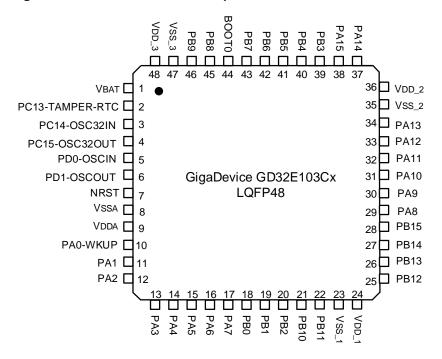
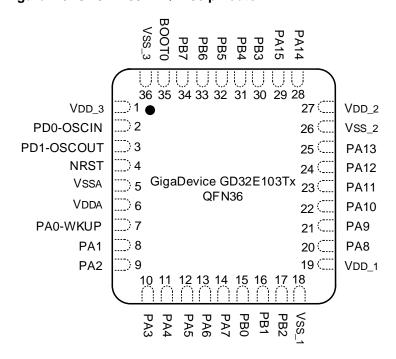




Figure 2-5. GD32E103Tx QFN36 pinouts



2.4. Memory map

Table 2-2. GD32E103xx memory map

Pre-defined regions	Bus	Address	Peripherals
External device		0xA000 0000 - 0xA000 0FFF	EXMC - SWREG
		0x9000 0000 - 0x9FFF FFFF	Reserved
External RAM	AHB3	0x7000 0000 - 0x8FFF FFFF	Reserved
External RAIVI		0x6000 0000 - 0x63FF FFFF	EXMC -
		0x6000 0000 - 0x63FF FFFF	NOR/PSRAM/SRAM
		0x5000 0000 - 0x5003 FFFF	USBFS
	AHB1	0x4008 0000 - 0x4FFF FFFF	Reserved
		0x4004 0000 - 0x4007 FFFF	Reserved
		0x4002 BC00 - 0x4003 FFFF	Reserved
		0x4002 B000 - 0x4002 BBFF	Reserved
		0x4002 A000 - 0x4002 AFFF	Reserved
Peripheral		0x4002 8000 - 0x4002 9FFF	Reserved
		0x4002 6800 - 0x4002 7FFF	Reserved
		0x4002 6400 - 0x4002 67FF	Reserved
		0x4002 6000 - 0x4002 63FF	Reserved
		0x4002 5000 - 0x4002 5FFF	Reserved
		0x4002 4000 - 0x4002 4FFF	Reserved
		0x4002 3C00 - 0x4002 3FFF	Reserved



!		OD32L I	USXX DataSheet
Pre-defined	Bus	Address	Peripherals
regions			•
		0x4002 3800 - 0x4002 3BFF	Reserved
		0x4002 3400 - 0x4002 37FF	Reserved
		0x4002 3000 - 0x4002 33FF	CRC
		0x4002 2C00 - 0x4002 2FFF	Reserved
		0x4002 2800 - 0x4002 2BFF	Reserved
		0x4002 2400 - 0x4002 27FF	Reserved
		0x4002 2000 - 0x4002 23FF	FMC
		0x4002 1C00 - 0x4002 1FFF	Reserved
		0x4002 1800 - 0x4002 1BFF	Reserved
		0x4002 1400 - 0x4002 17FF	Reserved
		0x4002 1000 - 0x4002 13FF	RCU
		0x4002 0C00 - 0x4002 0FFF	Reserved
		0x4002 0800 - 0x4002 0BFF	Reserved
		0x4002 0400 - 0x4002 07FF	DMA1
		0x4002 0000 - 0x4002 03FF	DMA0
		0x4001 8400 - 0x4001 FFFF	Reserved
		0x4001 8000 - 0x4001 83FF	Reserved
		0x4001 7C00 - 0x4001 7FFF	Reserved
		0x4001 7800 - 0x4001 7BFF	Reserved
		0x4001 7400 - 0x4001 77FF	Reserved
		0x4001 7000 - 0x4001 73FF	Reserved
		0x4001 6C00 - 0x4001 6FFF	Reserved
		0x4001 6800 - 0x4001 6BFF	Reserved
		0x4001 5C00 - 0x4001 67FF	Reserved
		0x4001 5800 - 0x4001 5BFF	Reserved
		0x4001 5400 - 0x4001 57FF	TIMER10
		0x4001 5000 - 0x4001 53FF	TIMER9
		0x4001 4C00 - 0x4001 4FFF	TIMER8
	APB2	0x4001 4800 - 0x4001 4BFF	Reserved
		0x4001 4400 - 0x4001 47FF	Reserved
		0x4001 4000 - 0x4001 43FF	Reserved
		0x4001 3C00 - 0x4001 3FFF	Reserved
		0x4001 3800 - 0x4001 3BFF	USART0
		0x4001 3400 - 0x4001 37FF	TIMER7
		0x4001 3000 - 0x4001 33FF	SPI0
		0x4001 2C00 - 0x4001 2FFF	TIMER0
		0x4001 2800 - 0x4001 2FF	ADC1
		0x4001 2400 - 0x4001 2FF	ADC1
I		0x4001 2000 - 0x4001 23FF	Reserved



		ODOZE I	OSXX Datasrice
Pre-defined regions	Bus	Address	Peripherals
		0x4001 1C00 - 0x4001 1FFF	Reserved
		0x4001 1800 - 0x4001 1BFF	GPIOE
		0x4001 1400 - 0x4001 17FF	GPIOD
		0x4001 1000 - 0x4001 13FF	GPIOC
		0x4001 0C00 - 0x4001 0FFF	GPIOB
		0x4001 0800 - 0x4001 0BFF	GPIOA
		0x4001 0400 - 0x4001 07FF	EXTI
		0x4001 0000 - 0x4001 03FF	AFIO
		0x4000 CC00 - 0x4000 FFFF	Reserved
		0x4000 C800 - 0x4000 CBFF	CTC
		0x4000 C400 - 0x4000 C7FF	Reserved
		0x4000 C000 - 0x4000 C3FF	Reserved
		0x4000 8000 - 0x4000 BFFF	Reserved
		0x4000 7C00 - 0x4000 7FFF	Reserved
		0x4000 7800 - 0x4000 7BFF	Reserved
		0x4000 7400 - 0x4000 77FF	DAC
		0x4000 7000 - 0x4000 73FF	PMU
		0x4000 6C00 - 0x4000 6FFF	BKP
		0x4000 6800 - 0x4000 6BFF	CAN1
		0x4000 6400 - 0x4000 67FF	CAN0
		0x4000 6000 - 0x4000 63FF	CAN SRAM 1K bytes
		0x4000 5C00 - 0x4000 5FFF	Reserved
		0x4000 5800 - 0x4000 5BFF	I2C1
	APB1	0x4000 5400 - 0x4000 57FF	I2C0
		0x4000 5000 - 0x4000 53FF	UART4
		0x4000 4C00 - 0x4000 4FFF	UART3
		0x4000 4800 - 0x4000 4BFF	USART2
		0x4000 4400 - 0x4000 47FF	USART1
		0x4000 4000 - 0x4000 43FF	Reserved
		0x4000 3C00 - 0x4000 3FFF	SPI2/I2S2
		0x4000 3800 - 0x4000 3BFF	SPI1/I2S1
		0x4000 3400 - 0x4000 37FF	Reserved
		0x4000 3000 - 0x4000 33FF	FWDGT
		0x4000 2C00 - 0x4000 2FFF	WWDGT
		0x4000 2800 - 0x4000 2BFF	RTC
		0x4000 2400 - 0x4000 27FF	Reserved
		0x4000 2000 - 0x4000 23FF	TIMER13
		0x4000 1C00 - 0x4000 1FFF	TIMER12
		0x4000 1800 - 0x4000 1BFF	TIMER11

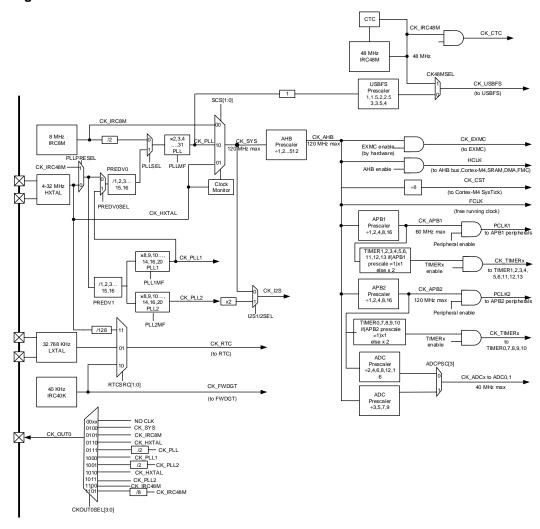


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Pre-defined regions	Bus	Address	Peripherals
		0x4000 1400 - 0x4000 17FF	TIMER6
		0x4000 1000 - 0x4000 13FF	TIMER5
		0x4000 0C00 - 0x4000 0FFF	TIMER4
		0x4000 0800 - 0x4000 0BFF	TIMER3
		0x4000 0400 - 0x4000 07FF	TIMER2
		0x4000 0000 - 0x4000 03FF	TIMER1
		0x2007 0000 - 0x3FFF FFFF	Reserved
		0x2006 0000 - 0x2006 FFFF	Reserved
		0x2003 0000 - 0x2005 FFFF	Reserved
SRAM	AHB	0x2002 0000 - 0x2002 FFFF	Reserved
SKAW	АПБ	0x2001 C000 - 0x2001 FFFF	
		0x2001 8000 - 0x2001 BFFF	- SRAM
		0x2000 5000 - 0x2001 7FFF	SKAW
		0x2000 0000 - 0x2000 4FFF	
		0x1FFF F810 - 0x1FFF FFFF	Reserved
		0x1FFF F800 - 0x1FFF F80F	Option Bytes
		0x1FFF F000 - 0x1FFF F7FF	
		0x1FFF C010 - 0x1FFF EFFF	Boot loader
		0x1FFF C000 - 0x1FFF C00F	Boot loader
		0x1FFF B000 - 0x1FFF BFFF	
		0x1FFF 7A10 - 0x1FFF AFFF	Reserved
		0x1FFF 7800 - 0x1FFF 7A0F	Reserved
		0x1FFF 0000 - 0x1FFF 77FF	Reserved
		0x1FFE C010 - 0x1FFE FFFF	Reserved
Code	AHB	0x1FFE C000 - 0x1FFE C00F	Reserved
Code	ALID	0x1001 0000 - 0x1FFE BFFF	Reserved
		0x1000 0000 - 0x1000 FFFF	Reserved
		0x083C 0000 - 0x0FFF FFFF	Reserved
		0x0830 0000 - 0x083B FFFF	Reserved
		0x0810 0000 - 0x082F FFFF	
		0x0802 0000 - 0x080F FFFF	Main Flash
		0x0800 0000 - 0x0801 FFFF	
		0x0030 0000 - 0x07FF FFFF	Reserved
		0x0010 0000 - 0x002F FFFF	Aliased to Main Flash or
		0x0002 0000 - 0x000F FFFF	Boot loader
		0x0000 0000 - 0x0001 FFFF	Door loadel



2.5. Clock tree

Figure 2-6. GD32E103xx clock tree



Legend:

HXTAL: 4 to 32 MHz High Speed crystal oscillator LXTAL: 32,768 Hz Low Speed crystal oscillator

IRC8M: Internal 8 MHz RC oscillator IRC40K: Internal 40 KHz RC oscillator IRC48M: Internal 48 MHz RC oscillator

2.6. Pin definitions

Notes:

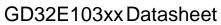
For GD32E103Rx LQFP64 $\scriptstyle \cdot$ GD32E103Cx LQFP48 and GD32E103Tx QFN36, V_{REF-} and V_{REF+} are internally connected to V_{SSA} and V_{DDA} respectively.



2.6.1. GD32E103Vx LQFP100 pin definitions

Table 2-3. GD32E103Vx LQFP100 pin definitions

		Pin	I/O	
Pin Name	Pins	Type ⁽¹⁾	Level ⁽²⁾	Functions description
PE2	1	I/O	5VT	Default: PE2
PEZ	ı	Ŋ	371	Alternate: TRACECK, EXMC_A23
PE3	2	I/O	5VT	Default: PE3
PES		Ŋ	371	Alternate: TRACED0, EXMC_A19
PE4	3	I/O	5VT	Default: PE4
F E 4	3	2)	371	Alternate: TRACED1, EXMC_A20
				Default: PE5
PE5	4	I/O	5VT	Alternate: TRACED2, EXMC_A21
				Remap: TIMER8_CH0
				Default: PE6
PE6	5	I/O	5VT	Alternate: TRACED3, EXMC_A22
				Remap: TIMER8_CH1
V_{BAT}	6	Р	-	Default: V _{BAT}
PC13-				Default: PC13
TAMPER-	7	I/O	-	Alternate: RTC_TAMPER
RTC				Alternate: NTO_TAINFER
PC14-	8	I/O	_	Default: PC14
OSC32IN	0	1/0	-	Alternate: OSC32IN
PC15- OSC32OU 9			-	Default: PC15
	9	I/O		Alternate: OSC32OUT
Т				Alternate: 03032001
Vss_5	10	Р	-	Default: V _{SS_5}
V_{DD_5}	11	Р	-	Default: V _{DD_5}
OSCIN	12	1	_	Default: OSCIN
OSCIIV	12	•	-	Remap: PD0
OSCOUT	13	0		Default: OSCOUT
030001	13)	-	Remap:PD1
NRST	14	I/O	-	Default: NRST
PC0	15	I/O	_	Default: PC0
1 00	10	2)		Alternate: ADC01_IN10
PC1	16	I/O	_	Default: PC1
101	10	i/O	_	Alternate: ADC01_IN11
PC2	17	I/O	_	Default: PC2
1 02	''	1/0	-	Alternate: ADC01_IN12
PC3	18	I/O	_	Default: PC3
103	10	1/0	_	Alternate: ADC01_IN13
Vssa	19	Р	-	Default: V _{SSA}
V_{REF}	20	Р	ı	Default: V _{REF-}



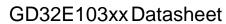


				GD32E T03xx Datasneet
Pin Name	Pin Name Pins Pin Type ⁽¹⁾		1/0	Functions description
			Level ⁽²⁾	·
V _{REF+}	21	Р	-	Default: V _{REF+}
V_{DDA}	22	Р	-	Default: V _{DDA}
				Default: PA0
PA0-WKUP	23	I/O	-	Alternate: WKUP, USART1_CTS, ADC01_IN0,
				TIMER1_CH0_ETI, TIMER4_CH0, TIMER7_ETI
				Default: PA1
PA1	24	I/O	-	Alternate: USART1_RTS, ADC01_IN1, TIMER4_CH1,
				TIMER1_CH1
				Default: PA2
PA2	25	I/O	-	Alternate: USART1_TX, TIMER4_CH2, ADC01_IN2,
				TIMER8_CH0, TIMER1_CH2, SPI0_IO2
				Default: PA3
PA3	26	I/O	-	Alternate: USART1_RX, TIMER4_CH3, ADC01_IN3,
				TIMER1_CH3, TIMER8_CH1, SPI0_IO3
V _{SS_4}	27	Р	-	Default: V _{SS_4}
V_{DD_4}	28	Р	-	Default: V _{DD_4}
		I/O	-	Default: PA4
	29			Alternate: SPI0_NSS, USART1_CK, DAC_OUT0,
PA4				ADC01_IN4
				Remap: SPI2_NSS, I2S2_WS
	30 I/O			Default: PA5
PA5		-	Alternate: SPI0_SCK, ADC01_IN5, DAC_OUT1	
				Default: PA6
				Alternate: SPI0_MISO, TIMER7_BKIN, ADC01_IN6,
PA6	31	I/O	-	TIMER2_CH0, TIMER12_CH0
				Remap: TIMER0_BKIN
				Default: PA7
				Alternate: SPI0_MOSI, TIMER7_CH0_ON, ADC01_IN7,
PA7	32	I/O	-	TIMER2_CH1, TIMER13_CH0
				Remap: TIMER0_CH0_ON
				Default: PC4
PC4	33	I/O	-	Alternate: ADC01_IN14
				Default: PC5
PC5	34	I/O	-	Alternate: ADC01_IN15
				Default: PB0
PB0	35	I/O	-	Alternate: ADC01_IN8, TIMER2_CH2, TIMER7_CH1_ON
				Remap: TIMER0_CH1_ON
				Default: PB1
PB1	36	I/O	-	Alternate: ADC01_IN9, TIMER2_CH3, TIMER7_CH2_ON
				Remap: TIMER0_CH2_ON
PB2	37	I/O	5VT	Default: PB2, BOOT1
			1	<u> </u>





		Din	VO SESSE TOSAX BATASTIC		
Pin Name	Pins	Pin Type ⁽¹⁾	Level ⁽²⁾	Functions description	
		- 71-		Default: PE7	
PE7	38	I/O	5VT	Alternate: EXMC_D4	
				Remap: TIMER0_ETI	
				Default: PE8	
PE8	39	I/O	5VT	Alternate: EXMC_D5	
				Remap: TIMER0_CH0_ON	
				Default: PE9	
PE9	40	I/O	5VT	Alternate: EXMC_D6	
				Remap: TIMER0_CH0	
				Default: PE10	
PE10	41	I/O	5VT	Alternate: EXMC_D7	
				Remap: TIMER0_CH1_ON	
				Default: PE11	
PE11	42	I/O	5VT	Alternate: EXMC_D8	
				Remap: TIMER0_CH1	
				Default: PE12	
PE12	43	I/O	5VT	Alternate: EXMC_D9	
				Remap: TIMER0_CH2_ON	
				Default: PE13	
PE13	44	I/O	5VT	Alternate: EXMC_D10	
				Remap: TIMER0_CH2	
				Default: PE14	
PE14	45	I/O	5VT	Alternate: EXMC_D11	
				Remap: TIMER0_CH3	
				Default: PE15	
PE15	46	I/O	5VT	Alternate: EXMC_D12	
				Remap: TIMER0_BKIN	
				Default: PB10	
PB10	47	I/O	5VT	Alternate: I2C1_SCL, USART2_TX	
				Remap: TIMER1_CH2	
				Default: PB11	
PB11	48	I/O	5VT	Alternate: I2C1_SDA, USART2_RX	
				Remap: TIMER1_CH3	
Vss_1	49	Р	-	Default: Vss_1	
V_{DD_1}	50	Р	-	Default: V _{DD_1}	
				Default: PB12	
PB12	51	I/O	5VT	Alternate: SPI1_NSS, I2S1_WS, I2C1_SMBA, USART2_CK,	
				TIMER0_BKIN, CAN1_RX	
				Default: PB13	
PB13	52	I/O	5VT	Alternate: SPI1_SCK, I2S1_CK, USART2_CTS,	
				TIMER0_CH0_ON, CAN1_TX, I2C1_TXFRAME	



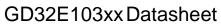


Pin Name	Pins	Pin	I/O	Functions description
		Type ⁽¹⁾	Level ⁽²⁾	·
				Default: PB14
PB14	53	I/O	5VT	Alternate: SPI1_MISO, USART2_RTS, TIMER0_CH1_ON,
				TIMER11_CH0
				Default: PB15
PB15	54	I/O	5VT	Alternate: SPI1_MOSI, I2S1_SD, TIMER0_CH2_ON,
				TIMER11_CH11
				Default: PD8
PD8	55	I/O	5VT	Alternate: EXMC_D13
				Remap: USART2_TX
				Default: PD9
PD9	56	I/O	5VT	Alternate: EXMC_D14
				Remap: USART2_RX
				Default: PD10
PD10	57	I/O	5VT	Alternate: EXMC_D15
				Remap: USART2_CK
				Default: PD11
PD11	58	I/O	5VT	Alternate: EXMC_A16
				Remap: USART2_CTS
				Default: PD12
PD12	59	I/O	5VT	Alternate: EXMC_A17
				Remap: TIMER3_CH0, USART2_RTS
				Default: PD13
PD13	60	I/O	5VT	Alternate: EXMC_A18
				Remap: TIMER3_CH1
				Default: PD14
PD14	61	I/O	5VT	Alternate: EXMC_D0
				Remap: TIMER3_CH2
				Default: PD15
PD15	62	I/O	5VT	Alternate: EXMC_D1
				Remap: TIMER3_CH3, CTC_SYNC
				Default: PC6
PC6	63	I/O	5VT	Alternate: I2S1_MCK, TIMER7_CH0
				Remap: TIMER2_CH0
				Default: PC7
PC7	64	I/O	5VT	Alternate: I2S2_MCK, TIMER7_CH1
		_		Remap: TIMER2_CH1
				Default: PC8
PC8	65	I/O	5VT	Alternate: TIMER7_CH2
				Remap: TIMER2_CH2





	Dis VO			
Pin Name	Pins	Pin	1/0	Functions description
		Type ⁽¹⁾	Level ⁽²⁾	D (11 DO)
DOO	00	1/0	5\ /T	Default: PC9
PC9	66	I/O	5VT	Alternate: TIMER7_CH3
				Remap: TIMER2_CH3
				Default: PA8
PA8	67	I/O	5VT	Alternate: USART0_CK, TIMER0_CH0, CK_OUT0, VCORE,
				USBFS_SOF, CTC_SYNC
PA9	68	I/O	5VT	Default: PA9
				Alternate: USART0_TX, TIMER0_CH1, USBFS_VBUS
PA10	69	I/O	5VT	Default: PA10
				Alternate: USART0_RX, TIMER0_CH2, USBFS_ID, V1REF
				Default: PA11
PA11	70	I/O	5VT	Alternate: USART0_CTS, CAN0_RX, USBFS_DM,
				TIMER0_CH3
				Default: PA12
PA12	71	I/O	5VT	Alternate: USART0_RTS, CAN0_TX, USBFS_DP,
				TIMER0_ETI
DA42	72	1/0	E\/T	Default: JTMS, SWDIO
PA13	12	I/O	5VT	Remap: PA13
NC	73	-	-	-
V _{SS_2}	74	Р	-	Default: Vss_2
V _{DD_2}	75	Р	-	Default: V _{DD_2}
5444		1/0	-> / -	Default: JTCK, SWCLK
PA14	76	I/O	5VT	Remap:PA14
				Default: JTDI
PA15	77	I/O	5VT	Alternate: SPI2_NSS, I2S2_WS
				Remap: TIMER1_CH0, TIMER1_ETI, PA15, SPI0_NSS
				Default: PC10
PC10	78	I/O	5VT	Alternate: UART3_TX
				Remap: USART2_TX, SPI2_SCK, I2S2_CK
				Default: PC11
PC11	79	I/O	5VT	Alternate: UART3_RX
				Remap: USART2_RX, SPI2_MISO
				Default: PC12
PC12	80	I/O	5VT	Alternate: UART4_TX
				Remap: USART2_CK, SPI2_MOSI, I2S2_SD
				Default: PD0
PD0	81	I/O	5VT	Alternate: EXMC_D2
				Remap: OSCIN, CANO_RX
				Default: PD1
PD1	82	I/O	5VT	Alternate: EXMC_D3
	52	., 0		Remap: OSCOUT, CAN0_TX
				ποπαρ. 000001, 0/1110_1/





Pin Name		GD32E 103XX DataSheet					
PD2	Pin Name	Pins			Functions description		
Alternate: TIMER2_ETI, UART4_RX	DDO	00	1/0	r\/T	Default: PD2		
PD3	PD2	83	1/0	501	Alternate: TIMER2_ETI, UART4_RX		
Remap: USART1_CTS					Default: PD3		
Default: PD4	PD3	84	I/O	5VT	Alternate: EXMC_CLK		
PD4					Remap: USART1_CTS		
Remap: USART1_RTS					Default: PD4		
Default: PD5	PD4	85	I/O	5VT	Alternate: EXMC_NOE		
PD5					Remap: USART1_RTS		
Remap: USART1_TX					Default: PD5		
Default: PD6	PD5	86	I/O	5VT	Alternate: EXMC_NWE		
PD6					Remap: USART1_TX		
Remap: USART1_RX					Default: PD6		
Default: PD7	PD6	87	I/O	5VT	Alternate: EXMC_NWAIT		
PD7 88 I/O 5VT Alternate: EXMC_NE0 Remap: USART1_CK PB3 89 I/O 5VT Alternate: SPI2_SCK, I2S2_CK Remap: TIMER1_CH1, PB3, TRACESWO, SPI0_SCK PB4 90 I/O 5VT Alternate: SPI2_MISO, I2C0_TXFRAME Remap: TIMER2_CH0, PB4, SPI0_MISO PB5 91 I/O - Alternate: I2C0_SMBA, SPI2_MOSI, I2S2_SD Remap: TIMER2_CH1, SPI0_MOSI, CAN1_RX PB6 92 I/O 5VT Alternate: I2C0_SCL, TIMER3_CH0 Remap: USART0_TX, CAN1_TX, SPI0_IO2 PB7 93 I/O 5VT Alternate: I2C0_SDA, TIMER3_CH1, EXMC_NL(NADV) Remap: USART0_RX, SPI0_IO3 BOOT0 94 I - Default: BOOT0 PB8 95 I/O 5VT Alternate: TIMER3_CH2, TIMER9_CH0 Remap: I2C0_SCL, CAN0_RX PB9 96 I/O 5VT Alternate: TIMER3_CH3, TIMER10_CH0 Remap: I2C0_SDA, CAN0_TX PE0 97 I/O 5VT Default: PE0					Remap: USART1_RX		
Remap: USART1_CK					Default: PD7		
Default: JTDO	PD7	88	I/O	5VT	Alternate: EXMC_NE0		
PB3					Remap: USART1_CK		
Remap: TIMER1_CH1, PB3, TRACESWO, SPI0_SCK					Default: JTDO		
Default: NJTRST	PB3	89	I/O	5VT	Alternate: SPI2_SCK, I2S2_CK		
PB4 90 I/O 5VT Alternate: SPI2_MISO, I2C0_TXFRAME Remap: TIMER2_CH0, PB4, SPI0_MISO PB5 91 I/O - Alternate: I2C0_SMBA, SPI2_MOSI, I2S2_SD Remap: TIMER2_CH1, SPI0_MOSI, CAN1_RX PB6 92 I/O 5VT Alternate: I2C0_SCL, TIMER3_CH0 Remap: USART0_TX, CAN1_TX, SPI0_IO2 PB7 93 I/O 5VT Alternate: I2C0_SDA, TIMER3_CH1, EXMC_NL(NADV) Remap: USART0_RX, SPI0_IO3 BOOT0 94 I - Default: BOOT0 Default: PB8 PB8 95 I/O 5VT Alternate: TIMER3_CH2, TIMER9_CH0 Remap: I2C0_SCL, CAN0_RX PB9 96 I/O 5VT Alternate: TIMER3_CH3, TIMER10_CH0 Remap: I2C0_SDA, CAN0_TX PE0 97 I/O 5VT Default: PE0					Remap: TIMER1_CH1, PB3, TRACESWO, SPI0_SCK		
Remap: TIMER2_CH0, PB4, SPI0_MISO					Default: NJTRST		
Default: PB5	PB4	90	I/O	5VT	Alternate: SPI2_MISO, I2C0_TXFRAME		
PB5 91 I/O - Alternate: I2C0_SMBA, SPI2_MOSI, I2S2_SD Remap: TIMER2_CH1, SPI0_MOSI, CAN1_RX PB6 92 I/O 5VT Alternate: I2C0_SCL, TIMER3_CH0 Remap: USART0_TX, CAN1_TX, SPI0_IO2 PB7 93 I/O 5VT Alternate: I2C0_SDA, TIMER3_CH1, EXMC_NL(NADV) Remap: USART0_RX, SPI0_IO3 BOOT0 94 I - Default: BOOT0 PB8 95 I/O 5VT Alternate: TIMER3_CH2, TIMER9_CH0 Remap: I2C0_SCL, CAN0_RX PB9 96 I/O 5VT Alternate: TIMER3_CH3, TIMER10_CH0 Remap: I2C0_SDA, CAN0_TX PE0 97 I/O 5VT Default: PB0					Remap: TIMER2_CH0, PB4, SPI0_MISO		
Remap: TIMER2_CH1, SPI0_MOSI, CAN1_RX					Default: PB5		
PB6 92 I/O 5VT Alternate: I2C0_SCL, TIMER3_CH0	PB5	91	I/O	-	Alternate: I2C0_SMBA, SPI2_MOSI, I2S2_SD		
PB6 92 I/O 5VT Alternate: I2C0_SCL, TIMER3_CH0					Remap: TIMER2_CH1, SPI0_MOSI, CAN1_RX		
Remap: USART0_TX, CAN1_TX, SPI0_IO2					Default: PB6		
Default: PB7	PB6	92	I/O	5VT	Alternate: I2C0_SCL, TIMER3_CH0		
PB7 93 I/O 5VT Alternate: I2C0_SDA, TIMER3_CH1, EXMC_NL(NADV) Remap: USART0_RX, SPI0_IO3 BOOT0 94 I - Default: BOOT0 PB8 95 I/O 5VT Alternate: TIMER3_CH2, TIMER9_CH0 Remap: I2C0_SCL, CAN0_RX Default: PB9 PB9 96 I/O 5VT Alternate: TIMER3_CH3, TIMER10_CH0 Remap: I2C0_SDA, CAN0_TX Default: PE0					Remap: USART0_TX, CAN1_TX, SPI0_IO2		
Remap: USART0_RX, SPI0_IO3					Default: PB7		
BOOT0 94 1 - Default: BOOT0	PB7	93	I/O	5VT	Alternate: I2C0_SDA, TIMER3_CH1, EXMC_NL(NADV)		
PB8 95 I/O 5VT Alternate: TIMER3_CH2, TIMER9_CH0 Remap: I2C0_SCL, CAN0_RX Default: PB9 PB9 96 I/O 5VT Alternate: TIMER3_CH3, TIMER10_CH0 Remap: I2C0_SDA, CAN0_TX Default: PE0					Remap: USART0_RX, SPI0_IO3		
PB8 95 I/O 5VT Alternate: TIMER3_CH2, TIMER9_CH0	воото	94	I	-	Default: BOOT0		
Remap: I2C0_SCL, CAN0_RX					Default: PB8		
PB9 96 I/O 5VT Alternate: TIMER3_CH3, TIMER10_CH0 Remap: I2C0_SDA, CAN0_TX PE0 97 I/O 5VT Default: PE0	PB8	95	I/O	5VT	Alternate: TIMER3_CH2, TIMER9_CH0		
PB9 96 I/O 5VT Alternate: TIMER3_CH3, TIMER10_CH0 Remap: I2C0_SDA, CAN0_TX PE0 97 I/O 5VT Default:PE0					Remap: I2C0_SCL, CAN0_RX		
Remap: I2C0_SDA, CAN0_TX		1			Default: PB9		
PE0 97 I/O 5VT Default:PE0	PB9	96	I/O	5VT	Alternate: TIMER3_CH3, TIMER10_CH0		
PE0 97 I/O 5VT					Remap: I2C0_SDA, CAN0_TX		
PEU 97 I/O 5V I Alternate: TIMER3_ETI, EXMC_NBL0	P=0	6-	1/0	5) (7	Default:PE0		
	PE0	97	I/O	5VT	Alternate: TIMER3_ETI, EXMC_NBL0		



Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
PE1	98	I/O	5VT	Default: PE1 Alternate: EXMC_NBL1
V _{SS_3}	99	Р	-	Default: V _{SS_3}
V _{DD_3}	100	Р	-	Default: V _{DD_3}

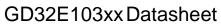
Notes:

- 1. Type: I= input, O = output, P = power.
- 2. I/O Level: 5VT = 5V tolerant.
- 3. Functions are available in GD32E103xx devices.

2.6.2. GD32E103Rx LQFP64 pin definitions

Table 2-4. GD32E103Rx LQFP64 pin definitions

Pin Name	Pins	Pin	I/O	Functions description
Pin Name	Pins	Type ⁽¹⁾	Level ⁽²⁾	Functions description
VBAT	1	Р	-	Default: V _{BAT}
PC13- TAMPER- RTC	2	I/O	-	Default: PC13 Alternate: RTC_TAMPER
PC14- OSC32IN	3	I/O	-	Default: PC14 Alternate:OSC32IN
PC15- OSC32OUT	4	I/O	-	Default: PC15 Alternate:OSC32OUT
PD0-OSCIN	5	I	-	Default: OSCIN Remap: PD0
PD1- OSCOUT	6	0	-	Default: OSCOUT Remap: PD1
NRST	7	I/O	-	Default: NRST
PC0	8	I/O	-	Default: PC0 Alternate: ADC01_IN10
PC1	9	I/O	-	Default: PC1 Alternate: ADC01_IN11
PC2	10	I/O	-	Default: PC2 Alternate: ADC01_IN12
PC3	11	1/0	-	Default: PC3 Alternate: ADC01_IN13
Vssa	12	Р	-	Default: V _{SSA}
V _{DDA}	13	Р	-	Default: V _{DDA}
PA0-WKUP	14	I/O	-	Default: PA0 Alternate: WKUP, USART1_CTS, ADC01_IN0, TIMER1_CH0_ETI, TIMER4_CH0, TIMER7_ETI
PA1	15	I/O	-	Default: PA1



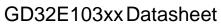


				GD32E 103XX Datasitee
Pin Name	Pins	Pin	I/O	Functions description
		Type ⁽¹⁾	Level ⁽²⁾	
				Alternate: USART1_RTS, ADC01_IN1, TIMER4_CH1,
				TIMER1_CH1
				Default: PA2
PA2	16	I/O	-	Alternate: USART1_TX, TIMER4_CH2, ADC01_IN2,
				TIMER8_CH0, TIMER1_CH2, SPI0_IO2
				Default: PA3
PA3	17	I/O	-	Alternate: USART1_RX, TIMER4_CH3, ADC01_IN3,
				TIMER1_CH3, TIMER8_CH1, SPI0_IO3
Vss_4	18	Р	-	Default: V _{SS_4}
V _{DD_4}	19	Р	-	Default: V _{DD_4}
				Default: PA4
PA4	20	I/O	_	Alternate: SPI0_NSS, USART1_CK, DAC_OUT0,
FA4	20	1/0	-	ADC01_IN4
				Remap: SPI2_NSS, I2S2_WS
PA5	21	I/O		Default: PA5
PAS	21	1/0	-	Alternate: SPI0_SCK, ADC01_IN5, DAC_OUT1
				Default: PA6
DAG	20	1/0		Alternate: SPI0_MISO, TIMER7_BKIN, ADC01_IN6,
PA6	22	I/O	-	TIMER2_CH0, TIMER12_CH0
				Remap: TIMER0_BKIN
				Default: PA7
DAZ	22	1/0		Alternate: SPI0_MOSI, TIMER7_CH0_ON, ADC01_IN7,
PA7	23	I/O	-	TIMER2_CH1, TIMER13_CH0
				Remap: TIMER0_CH0_ON
DO4	0.4	1/0		Default: PC4
PC4	24	1/0	-	Alternate: ADC01_IN14
DOS	0.5	1/0		Default: PC5
PC5	25	1/0	-	Alternate: ADC01_IN15
				Default: PB0
PB0	26	I/O	-	Alternate: ADC01_IN8, TIMER2_CH2, TIMER7_CH1_ON
				Remap: TIMER0_CH1_ON
				Default: PB1
PB1	27	I/O	-	Alternate: ADC01_IN9, TIMER2_CH3, TIMER7_CH2_ON
				Remap: TIMER0_CH2_ON
PB2	28	I/O	5VT	Default: PB2, BOOT1
				Default: PB10
PB10	29	I/O	5VT	Alternate: I2C1_SCL, USART2_TX
				Remap: TIMER1_CH2
				Default: PB11
PB11	30	I/O	5VT	Alternate: I2C1_SDA, USART2_RX
PB1 PB2 PB10	27 28 29	I/O I/O	5VT	Default: PC4 Alternate: ADC01_IN14 Default: PC5 Alternate: ADC01_IN15 Default: PB0 Alternate: ADC01_IN8, TIMER2_CH2, TIMER7_CH1_ON Remap: TIMER0_CH1_ON Default: PB1 Alternate: ADC01_IN9, TIMER2_CH3, TIMER7_CH2_ON Remap: TIMER0_CH2_ON Default: PB2, BOOT1 Default: PB10 Alternate: I2C1_SCL, USART2_TX Remap: TIMER1_CH2 Default: PB11





Pin I/O		ODSZE 103XX Datasiteet			
	Pin Name	Pins	Type ⁽¹⁾	Level ⁽²⁾	Functions description
ŀ	V _{SS_1}	31	P	-	Default: Vss_1
F	V_{DD_1}	32	Р	-	Default: V _{DD_1}
ŀ					Default: PB12
	PB12	33	I/O	5VT	Alternate: SPI1_NSS, I2S1_WS, I2C1_SMBA, USART2_CK,
					TIMER0_BKIN, CAN1_RX
ŀ					Default: PB13
	PB13	34	I/O	5VT	Alternate: SPI1_SCK, I2S1_CK, USART2_CTS,
					TIMER0_CH0_ON, CAN1_TX, I2C1_TXFRAME
					Default: PB14
	PB14	35	I/O	5VT	Alternate: SPI1_MISO, USART2_RTS, TIMER0_CH1_ON,
					TIMER11_CH0
					Default: PB15
	PB15	36	I/O	5VT	Alternate: SPI1_MOSI, I2S1_SD, TIMER0_CH2_ON,
					TIMER11_CH11
					Default: PC6
	PC6	37	I/O	5VT	Alternate: I2S1_MCK, TIMER7_CH0
					Remap: TIMER2_CH0
					Default: PC7
	PC7	38	I/O	5VT	Alternate: I2S2_MCK, TIMER7_CH1
				Remap: TIMER2_CH1	
					Default: PC8
	PC8	39	I/O	5VT	Alternate: TIMER7_CH2
					Remap: TIMER2_CH2
					Default: PC9
	PC9	40	I/O	5VT	Alternate: TIMER7_CH3
ļ					Remap: TIMER2_CH3
					Default: PA8
	PA8	41	I/O	5VT	Alternate: USART0_CK, TIMER0_CH0, CK_OUT0, VCORE,
ļ					USBFS_SOF, CTC_SYNC
	PA9	42	I/O	5VT	Default: PA9
ļ					Alternate: USART0_TX, TIMER0_CH1, USBFS_VBUS
	PA10	43	I/O	5VT	Default: PA10
Ļ					Alternate: USARTO_RX, TIMERO_CH2, USBFS_ID, V1REF
	PA11	44	I/O	5VT	Default: PA11 Alternate: USART0_CTS, CAN0_RX, USBFS_DM,
	FAII	44	1/0	3 7 1	TIMERO_CH3
ŀ					Default: PA12
	PA12	45	I/O	5VT	Alternate: USART0_RTS, CAN0_TX, USBFS_DP,
	. / \ / \	.5	,, 0	3 7 1	TIMERO_ETI
ŀ					Default: JTMS, SWDIO
	PA13	46	I/O	5VT	Remap: PA13
L					• -





GD32E 103XX Datasileet				
Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
Vss 2	47	P	-	Default: Vss_2
V _{DD 2}	48	Р	-	Default: V _{DD_2}
				Default: JTCK, SWCLK
PA14	49	I/O	5VT	Remap:PA14
				Default: JTDI
PA15	50	I/O	5VT	Alternate: SPI2_NSS, I2S2_WS
				Remap: TIMER1_CH0_ETI, TIMER1_ETI, PA15, SPI0_NSS
				Default: PC10
PC10	51	I/O	5VT	Alternate: UART3_TX
				Remap: USART2_TX, SPI2_SCK, I2S2_CK
				Default: PC11
PC11	52	I/O	5VT	Alternate: UART3_RX
				Remap: USART2_RX, SPI2_MISO
				Default: PC12
PC12	53	I/O	5VT	Alternate: UART4_TX
				Remap: USART2_CK, SPI2_MOSI, I2S2_SD
				Default: PD2
PD2	54	I/O	5VT	Alternate: TIMER2_ETI, UART4_RX
				Default: JTDO
PB3	55	I/O	5VT	Alternate: SPI2_SCK, I2S2_CK
				Remap: TIMER1_CH1, PB3, TRACESWO, SPI0_SCK
				Default: NJTRST
PB4	56	I/O	5VT	Alternate: SPI2_MISO, I2C0_TXFRAME
				Remap: TIMER2_CH0, PB4, SPI0_MISO
				Default: PB5
PB5	57	I/O	-	Alternate: I2C0_SMBA, SPI2_MOSI, I2S2_SD
				Remap: TIMER2_CH1, SPI0_MOSI, CAN1_RX
				Default: PB6
PB6	58	I/O	5VT	Alternate: I2C0_SCL, TIMER3_CH0
				Remap: USART0_TX, CAN1_TX, SPI0_IO2
				Default: PB7
PB7	59	I/O	5VT	Alternate: I2C0_SDA, TIMER3_CH1
				Remap: USART0_RX, SPI0_IO3
воото	60	I	-	Default: BOOT0
				Default: PB8
PB8	61	I/O	5VT	Alternate: TIMER3_CH2, TIMER9_CH0
				Remap: I2C0_SCL, CAN0_RX
				Default: PB9
PB9	62	I/O	5VT	Alternate: TIMER3_CH3, TIMER10_CH0
				Remap: I2C0_SDA, CAN0_TX
V _{SS_3}	63	Р	ı	Default: Vss_3



Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
V_{DD_3}	64	Р	-	Default: V _{DD_3}

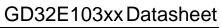
Notes:

- 1. Type: I= input, O = output, P = power.
- 2. I/O Level: 5VT = 5V tolerant.
- 3. Functions are available in GD32E103xx devices.

2.6.3. GD32E103Cx LQFP48 pin definitions

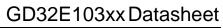
Table 2-5. GD32E103Cx LQFP48 pin definitions

Table 2-3. GD.		Pin	1/0	
Pin Name	Pins	Type ⁽¹⁾	Level ⁽²⁾	Functions description
V_{BAT}	1	Р	-	Default: V _{BAT}
PC13- TAMPER- RTC	2	I/O	-	Default: PC13 Alternate: RTC_TAMPER
PC14- OSC32IN	3	I/O	-	Default: PC14 Alternate:OSC32IN
PC15- OSC32OUT	4	I/O	-	Default: PC15 Alternate:OSC32OUT
PD0-OSCIN	5	I	-	Default: OSCIN Remap: PD0
PD1-OSCOUT	6	0	-	Default: OSCOUT Remap: PD1
NRST	7	I/O	-	Default: NRST
Vssa	8	Р	-	Default: V _{SSA}
V _{DDA}	9	Р	-	Default: V _{DDA}
PA0-WKUP	10	I/O	-	Default: PA0 Alternate: WKUP, USART1_CTS, ADC01_IN0, TIMER1_CH0_ETI, TIMER4_CH0, TIMER7_ETI
PA1	11	I/O	-	Default: PA1 Alternate: USART1_RTS, ADC01_IN1, TIMER4_CH1, TIMER1_CH1
PA2	12	I/O	-	Default: PA2 Alternate: USART1_TX, TIMER4_CH2, ADC01_IN2, TIMER8_CH0, TIMER1_CH2, SPI0_IO2
PA3	13	I/O	-	Default: PA3 Alternate: USART1_RX, TIMER4_CH3, ADC01_IN3, TIMER1_CH3, TIMER8_CH1, SPI0_IO3
PA4	14	I/O	-	Default: PA4 Alternate: SPI0_NSS, USART1_CK, DAC_OUT0, ADC01_IN4





		Pin	I/O			
Pin Name	Pins	Type ⁽¹⁾	Level ⁽²⁾	Functions description		
		Туре	Level	Remap: SPI2_NSS, I2S2_WS		
				Default: PA5		
PA5	PA5 15	I/O	-	Alternate: SPI0_SCK, ADC01_IN5, DAC_OUT1		
				Default: PA6		
				Alternate: SPI0_MISO, TIMER7_BKIN, ADC01_IN6,		
PA6	16	I/O	-	TIMER2_CH0, TIMER12_CH0		
				Remap: TIMER0_BKIN		
				Default: PA7		
		I/O		Alternate: SPI0_MOSI, TIMER7_CH0_ON, ADC01_IN7,		
PA7	17		-	TIMER2_CH1, TIMER13_CH0		
				Remap: TIMER0_CH0_ON		
				Default: PB0		
PB0	18	I/O	-	Alternate: ADC01_IN8, TIMER2_CH2, TIMER7_CH1_ON		
				Remap: TIMER0_CH1_ON		
				Default: PB1		
PB1	19	I/O	-	Alternate: ADC01_IN9, TIMER2_CH3, TIMER7_CH2_ON		
				Remap: TIMER0_CH2_ON		
PB2	20	I/O	5VT	Default: PB2, BOOT1		
	21	I/O		Default: PB10		
PB10				Alternate: I2C1_SCL, USART2_TX		
				Remap: TIMER1_CH2		
				Default: PB11		
PB11	22	I/O		Alternate: I2C1_SDA, USART2_RX		
				Remap: TIMER1_CH3		
Vss_1	23	Р	-	Default: Vss_1		
V _{DD_1}	24	Р	-	Default: V _{DD_1}		
				Default: PB12		
PB12	25	I/O		Alternate: SPI1_NSS, I2S1_WS, I2C1_SMBA,		
				USART2_CK, TIMER0_BKIN, CAN1_RX		
	26	I/O	5VT	Default: PB13		
PB13				Alternate: SPI1_SCK, I2S1_CK, USART2_CTS,		
				TIMER0_CH0_ON, CAN1_TX, I2C1_TXFRAME		
PB14	27	I/O		Default: PB14		
				Alternate: SPI1_MISO, USART2_RTS,		
				TIMER0_CH1_ON, TIMER11_CH0		
PB15				Default: PB15		
	28	I/O	5VT	Alternate: SPI1_MOSI, I2S1_SD, TIMER0_CH2_ON,		
				TIMER11_CH11		
		I/O	5VT	Default: PA8		
PA8	29			Alternate: USART0_CK, TIMER0_CH0, CK_OUT0,		
				VCORE, USBFS_SOF, CTC_SYNC		





				ODSZE TOSAK Datasneet		
Pin Name	Pins	Pin	1/0	Functions description		
		Type ⁽¹⁾	Level ⁽²⁾			
PA9	30	I/O	5VT	Default: PA9		
				Alternate: USART0_TX, TIMER0_CH1, USBFS_VBUS		
				Default: PA10		
PA10	31	I/O	5VT	Alternate: USART0_RX, TIMER0_CH2, USBFS_ID,		
				V1REF		
				Default: PA11		
PA11	32	I/O	5VT	Alternate: USART0_CTS, CAN0_RX, USBFS_DM,		
				TIMER0_CH3		
				Default: PA12		
PA12	33	I/O	5VT	Alternate: USART0_RTS, CAN0_TX, USBFS_DP,		
				TIMER0_ETI		
PA13	34	I/O	5VT	Default: JTMS, SWDIO		
1 7 13	J- -	1/0	3 7 1	Remap: PA13		
Vss_2	35	Р	-	Default: V _{SS_2}		
V_{DD_2}	36	Р	-	Default: V _{DD_2}		
PA14	37	I/O	5VT	Default: JTCK, SWCLK		
FA14	31	1/0	371	Remap:PA14		
	38	I/O	5VT	Default: JTDI		
PA15				Alternate: SPI2_NSS, I2S2_WS		
PAIS				Remap: TIMER1_CH0_ETI, TIMER1_ETI, PA15,		
				SPI0_NSS		
	39	I/O	5VT	Default: JTDO		
PB3				Alternate: SPI2_SCK, I2S2_CK		
				Remap: TIMER1_CH1, PB3, TRACESWO, SPI0_SCK		
	40	I/O		Default: NJTRST		
PB4				Alternate: SPI2_MISO, I2C0_TXFRAME		
				Remap: TIMER2_CH0, PB4, SPI0_MISO		
	41	I/O	-	Default: PB5		
PB5				Alternate: I2C0_SMBA, SPI2_MOSI, I2S2_SD		
				Remap: TIMER2_CH1, SPI0_MOSI, CAN1_RX		
	42	I/O		Default: PB6		
PB6				Alternate: I2C0_SCL, TIMER3_CH0		
				Remap: USART0_TX, CAN1_TX, SPI0_IO2		
PB7	43	I/O	5VT	Default: PB7		
				Alternate: I2C0_SDA, TIMER3_CH1		
				Remap: USART0_RX, SPI0_IO3		
воото	44	I	-	Default: BOOT0		
				Default: PB8		
PB8	45	I/O	5VT	Alternate: TIMER3_CH2, TIMER9_CH0		
				Remap: I2C0_SCL, CAN0_RX		
PB9	46	I/O	5VT	Default: PB9		



Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
				Alternate: TIMER3_CH3, TIMER10_CH0
				Remap: I2C0_SDA, CAN0_TX
V _{SS_3}	47	Р	-	Default: V _{SS_3}
V _{DD_3}	48	Р	-	Default: V _{DD_3}

Notes:

- 1. Type: I= input, O = output, P = power.
- 2. I/O Level: 5VT = 5V tolerant.
- 3. Functions are available in GD32E103xx devices.

2.6.4. GD32E103Tx QFN36 pin definitions

Table 2-6. GD32E103Tx LQFP36 pin definitions

D' N	Pins	Pin	I/O	Functions description
Pin Name		Type ⁽¹⁾	Level ⁽²⁾	
PD0-OSCIN	2	I	-	Default: OSCIN
				Remap: PD0
DD4 OCCOUR	3	0	-	Default: OSCOUT
PD1-OSCOUT				Remap: PD1
NRST	4	I/O	-	Default: NRST
Vssa	5	Р	-	Default: V _{SSA}
V _{DDA}	6	Р	-	Default: V _{DDA}
				Default: PA0
PA0-WKUP	7	I/O	-	Alternate: WKUP, USART1_CTS, ADC01_IN0,
				TIMER1_CH0_ETI, TIMER4_CH0, TIMER7_ETI
	8	I/O	-	Default: PA1
PA1				Alternate: USART1_RTS, ADC01_IN1,
				TIMER4_CH1, TIMER1_CH1
	9	I/O	-	Default: PA2
PA2				Alternate: USART1_TX, TIMER4_CH2,
PAZ				ADC01_IN2, TIMER8_CH0, TIMER1_CH2,
				SPI0_IO2
	10	I/O	-	Default: PA3
PA3				Alternate: USART1_RX, TIMER4_CH3,
PAS				ADC01_IN3, TIMER1_CH3, TIMER8_CH1,
				SPI0_IO3
	_	I/O	-	Default: PA4
PA4	11			Alternate: SPI0_NSS, USART1_CK, DAC_OUT0,
				ADC01_IN4
PA5	12	I/O	-	Default: PA5
PAD				Alternate: SPI0_SCK, ADC01_IN5, DAC_OUT1
PA6	13	I/O	-	Default: PA6



		Pin	I/O	
Pin Name	Pins	Type ⁽¹⁾	Level ⁽²⁾	Functions description
				Alternate: SPI0_MISO, TIMER7_BKIN,
				ADC01_IN6, TIMER2_CH0, TIMER12_CH0
				Remap: TIMER0_BKIN
				Default: PA7
PA7	14	I/O		Alternate: SPI0_MOSI, TIMER7_CH0_ON,
PAI	14	1/0	-	ADC01_IN7, TIMER2_CH1, TIMER13_CH0
				Remap: TIMER0_CH0_ON
		1/0	-	Default: PB0
DDO	15			Alternate: ADC01_IN8, TIMER2_CH2,
PB0	15	I/O		TIMER7_CH1_ON
				Remap: TIMER0_CH1_ON
				Default: PB1
DD4	4.0	1/0		Alternate: ADC01_IN9, TIMER2_CH3,
PB1	16	I/O	-	TIMER7_CH2_ON
				Remap: TIMER0_CH2_ON
PB2	17	I/O	5VT	Default: PB2, BOOT1
V _{SS_1}	18	Р	-	Default: V _{SS_1}
V_{DD_1}	19	Р	-	Default: V _{DD_1}
				Default: PA8
PA8	20	I/O	5VT	Alternate: USART0_CK, TIMER0_CH0, CK_OUT0,
				VCORE, USBFS_SOF, CTC_SYNC
				Default: PA9
PA9	21	I/O	5VT	Alternate: USART0_TX, TIMER0_CH1,
				USBFS_VBUS
				Default: PA10
PA10	22	I/O	5VT	Alternate: USART0_RX, TIMER0_CH2, USBFS_ID,
				V1REF
				Default: PA11
PA11	23	I/O	5VT	Alternate: USART0_CTS, CAN0_RX, USBFS_DM,
				TIMER0_CH3
				Default: PA12
PA12	24	I/O	5VT	Alternate: USART0_RTS, CAN0_TX, USBFS_DP,
				TIMER0_ETI
PA13		I/O	5VT	Default: JTMS, SWDIO
	25			Remap: PA13
Vss_2	26	Р	-	Default: Vss_2
V _{DD_2}	27	Р	-	Default: V _{DD_2}
				Default: JTCK, SWCLK
PA14	28	I/O	5VT	Remap:PA14
PA15	29	I/O	5VT	Default: JTDI
	1			



Pin Name	Pins	Pin Type ⁽¹⁾	I/O Level ⁽²⁾	Functions description
				Remap: TIMER1_CH0_ETI, TIMER1_ETI, PA15,
				SPI0_NSS
				Default: JTDO
PB3	30	I/O	5VT	Remap: TIMER1_CH1, PB3, TRACESWO,
				SPI0_SCK
				Default: NJTRST
PB4	31	I/O	5VT	Alternate: I2C0_TXFRAME
				Remap: TIMER2_CH0, PB4, SPI0_MISO
				Default: PB5
PB5	32	I/O	-	Alternate: I2C0_SMBA
				Remap: TIMER2_CH1, SPI0_MOSI, CAN1_RX
				Default: PB6
PB6	33	I/O	5VT	Alternate: I2C0_SCL, TIMER3_CH0
				Remap: USART0_TX, CAN1_TX, SPI0_IO2
				Default: PB7
PB7	34	I/O	5VT	Alternate: I2C0_SDA, TIMER3_CH1
				Remap: USART0_RX, SPI0_IO3
воото	35	I	-	Default: BOOT0
V _{SS_3}	36	Р	-	Default: V _{SS_3}
V_{DD_3}	1	Р	-	Default: V _{DD_3}

Notes:

- 1. Type: I= input, O = output, P = power.
- 2. I/O Level: 5VT = 5V tolerant.
- 3. Functions are available in GD32E103xx devices.



3. Functional description

3.1. ARM[®] Cortex[™]-M4 core

The ARM® Cortex®-M4 processor is a high performance embedded processor with DSP instructions which allow efficient signal processing and complex algorithm execution. It brings an efficient, easy-to-use blend of control and signal processing capabilities to meet the digital signal control markets demand. The processor is highly configurable enabling a wide range of implementations from those requiring floating point operations, memory protection and powerful trace technology to cost sensitive devices requiring minimal area, while delivering outstanding computational performance and an advanced system response to interrupts.

32-bit ARM® Cortex®-M4 processor core

- Up to 120 MHz operation frequency
- Single-cycle multiplication and hardware divider
- Floating Point Unit (FPU)
- Integrated DSP instructions
- Integrated Nested Vectored Interrupt Controller (NVIC)
- 24-bit SysTick timer

The Cortex®-M4 processor is based on the ARMv7-M architecture and supports both Thumb and Thumb-2 instruction sets. Some system peripherals listed below are also provided by Cortex®-M4:

- Internal Bus Matrix connected with ICode bus, DCode bus, system bus, Private Peripheral Bus (PPB) and debug accesses (AHB-AP)
- Nested Vectored Interrupt Controller (NVIC)
- Flash Patch and Breakpoint (FPB)
- Data Watchpoint and Trace (DWT)
- Instrument Trace Macrocell (ITM)
- Serial Wire JTAG Debug Port (SWJ-DP)
- Trace Port Interface Unit (TPIU)

3.2. On-chip memory

- Up to 128 Kbytes of Flash memory
- Up to 32 KB of SRAM

The ARM® Cortex®-M4 processor is structured in Harvard architecture which can use separate buses to fetch instructions and load/store data. 128 Kbytes of inner Flash at most, which includes code Flash that available for storing programs and data, and accessed (R/W) at CPU clock speed with zero wait states. An extra data Flash is also included for storing data mainly. *Table 2-2. GD32E103xx memory map* shows the memory of the GD32E103xx series of devices, including Flash, SRAM, peripheral, and other pre-defined regions.



3.3. Clock, reset and supply management

- Internal 8 MHz factory-trimmed RC and external 4 to 32 MHz crystal oscillator
- Internal 48 MHz RC oscillator
- Internal 40 KHz RC calibrated oscillator and external 32.768 KHz crystal oscillator
- 1.71 to 3.6 V application supply and I/Os
- Supply Supervisor: POR (Power On Reset), PDR (Power Down Reset), and low voltage detector (LVD)

The Clock Control Unit (CCU) provides a range of oscillator and clock functions. These include internal RC oscillator and external crystal oscillator, high speed and low speed two types. Several prescalers allow the frequency configuration of the AHB and two APB domains. The maximum frequency of the two AHB domains are 120MHz. The maximum frequency of the two APB domains including APB1 is 60 MHz and APB2 is 120 MHz. See *Figure 2-6. GD32E103xx clock tree* for details on the clock tree.

The Reset Control Unit (RCU) controls three kinds of reset: system reset resets the processor core and peripheral IP components. Power-on reset (POR) and power-down reset (PDR) are always active, and ensures proper operation starting from 1.66V/down to 1.62V. The device remains in reset mode when VDD is below a specified threshold. The embedded low voltage detector (LVD) monitors the power supply, compares it to the voltage threshold and generates an interrupt as a warning message for leading the MCU into security.

Power supply schemes:

- V_{DD} range: 1.71 to 3.6 V, external power supply for I/Os and the internal regulator. Provided externally through V_{DD} pins.
- VDDA range: 1.71 to 3.6 V, external analog power supplies for ADC, reset blocks, RCs and PLL. VDDA and VssA must be connected to VDD and Vss, respectively.
- VBAT range: 1.71 to 3.6 V, power supply for RTC, external clock 32.768 KHz oscillator and backup registers (through power switch) when VDD is not present.

3.4. Boot modes

At startup, boot pins are used to select one of three boot options:

- Boot from main flash memory (default)
- Boot from system memory
- Boot from on-chip SRAM

In default condition, boot from main Flash memory is selected. The boot loader is located in the internal boot ROM memory (system memory). It is used to reprogram the Flash memory by using USART0 (PA9 and PA10).



3.5. Power saving modes

The MCU supports three kinds of power saving modes to achieve even lower power consumption. They are Sleep mode, Deep-sleep mode, and Standby mode. These operating modes reduce the power consumption and allow the application to achieve the best balance between the CPU operating time, speed and power consumption.

■ Sleep mode

In sleep mode, only the clock of CPU core is off. All peripherals continue to operate and any interrupt/event can wake up the system.

■ Deep-sleep mode

In deep-sleep mode, all clocks in the 1.2V domain are off, and all of the high speed crystal oscillator (IRC8M, IRC48M, HXTAL) and PLL are disabled. Only the contents of SRAM and registers are retained. Any interrupt or wakeup event from EXTI lines can wake up the system from the deep-sleep mode including the 16 external lines, the RTC alarm, the LVD output, and USB wakeup. When exiting the deep-sleep mode, the IRC8M is selected as the system clock.

Standby mode

In standby mode, the whole 1.2V domain is power off, the LDO is shut down, and all of IRC8M, IRC48M, HXTAL and PLL are disabled. The contents of SRAM and registers (except Backup Registers) are lost. There are four wakeup sources for the standby mode, including the external reset from NRST pin, the RTC, the FWDG reset, and the rising edge on WKUP pin.

3.6. Analog to digital converter (ADC)

- 12-bit SAR ADC's conversion rate is up to 3 MSPS
- 12-bit, 10-bit, 8-bit or 6-bit configurable resolution
- Hardware oversampling ratio adjustable from 2 to 256x improves resolution to 16-bit
- Input voltage range: V_{REF-} to V_{REF+}
- Temperature sensor

Up to two 12-bit 3 MSPS multi-channel ADCs are integrated in the device. It has a total of 18 multiplexed channels: 16 external channels, 1 channel for internal temperature sensor (V_{SENSE}), 1 channel for internal reference voltage (V_{REFINT}, V_{REFINT} = 1.2V). The input voltage range is from V_{REF} to V_{REF}. An on-chip hardware oversampling scheme improves performance while off-loading the related computational burden from the CPU. An analog watchdog block can be used to detect the channels, which are required to remain within a specific threshold window. A configurable channel management block can be used to perform conversions in single, continuous, scan or discontinuous mode to support more advanced use.

The ADC can be triggered from the events generated by the general level 0 timers (TIMERx, x=1, 2, 3) and the advanced timers (TIMER0 and TIMER7) with internal connection. The



temperature sensor can be used to generate a voltage that varies linearly with temperature. It is internally connected to the ADC_IN16 input channel which is used to convert the sensor output voltage in a digital value.

3.7. Digital to analog converter (DAC)

- 12-bit DAC with independent output channels
- 8-bit or 12-bit mode in conjunction with the DMA controller

The 12-bit buffered DAC is used to generate variable analog outputs. The DAC channels can be triggered by the timer or EXTI with DMA support. In dual DAC channel operation, conversions could be done independently or simultaneously. The maximum output value of the DAC is V_{REF+}.

3.8. DMA

- 7 channel DMA0 controller and 5 channel DMA1 controller
- Peripherals supported: Timers, ADC, SPIs, I2Cs, USARTs, DAC, I2S

The flexible general-purpose DMA controllers provide a hardware method of transferring data between peripherals and/or memory without intervention from the CPU, thereby freeing up bandwidth for other system functions. Three types of access method are supported: peripheral to memory, memory to peripheral, memory to memory.

Each channel is connected to fixed hardware DMA requests. The priorities of DMA channel requests are determined by software configuration and hardware channel number. Transfer size of source and destination are independent and configurable.

3.9. General-purpose inputs/outputs (GPIOs)

- Up to 80 fast GPIOs, all mappable on 16 external interrupt lines
- Analog input/output configurable
- Alternate function input/output configurable

There are up to 80 general purpose I/O pins (GPIO) in GD32E103xx, named PA0 ~ PA15, PB0 ~ PB15, PC0 ~ PC15, PD0 ~ PD15 and PE0 ~ PE15 to implement logic input/output functions. Each of the GPIO ports has related control and configuration registers to satisfy the requirements of specific applications. The external interrupts on the GPIO pins of the device have related control and configuration registers in the Interrupt/event controller (EXTI). The GPIO ports are pin-shared with other alternative functions (AFs) to obtain maximum flexibility on the package pins. Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. All GPIOs are high-current capable except for analog inputs.



3.10. Timers and PWM generation

- Two 16-bit advanced timer (TIMER0 & TIMER7), ten 16-bit general timers (TIMER1 ~ TIMER4, TIMER8 ~ TIMER13), and two 16-bit basic timer (TIMER5 & TIMER6)
- Up to 4 independent channels of PWM, output compare or input capture for each general timer and external trigger input
- 16-bit, motor control PWM advanced timer with programmable dead-time generation for output match
- Encoder interface controller with two inputs using quadrature decoder
- 24-bit SysTick timer down counter
- 2 watchdog timers (free watchdog timer and window watchdog timer)

The advanced timer (TIMER0 & TIMER7) can be used as a three-phase PWM multiplexed on 6 channels. It has complementary PWM outputs with programmable dead-time generation. It can also be used as a complete general timer. The 4 independent channels can be used for input capture, output compare, PWM generation (edge-aligned or center-aligned counting modes) and single pulse mode output. If configured as a general 16-bit timer, it has the same functions as the TIMERx timer. It can be synchronized with external signals or to interconnect with other general timers together which have the same architecture and features.

The general timer, can be used for a variety of purposes including general time, input signal pulse width measurement or output waveform generation such as a single pulse generation or PWM output, up to 4 independent channels for input capture/output compare. TIMER1 ~ TIMER4 is based on a 16-bit auto-reload up/downcounter and a 16-bit prescaler. TIMER8 ~ TIMER13 is based on a 16-bit auto-reload upcounter and a 16-bit prescaler. The general timer also supports an encoder interface with two inputs using quadrature decoder.

The basic timer, known as TIMER5 &TIMER6, are mainly used for DAC trigger generation. They can also be used as a simple 16-bit time base.

The GD32E103xx have two watchdog peripherals, free watchdog timer and window watchdog timer. They offer a combination of high safety level, flexibility of use and timing accuracy.

The free watchdog timer includes a 12-bit down-counting counter and an 8-bit prescaler. It is clocked from an independent 40 KHz internal RC and as it operates independently of the main clock, it can operate in deep-sleep and standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout management.

The window watchdog timer is based on a 7-bit down counter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early wakeup interrupt capability and the counter can be frozen in debug mode.

The SysTick timer is dedicated for OS, but could also be used as a standard down counter. It features:



- A 24-bit down counter
- Auto reload capability
- Maskable system interrupt generation when the counter reaches 0
- Programmable clock source

3.11. Real time clock (RTC)

- 32-bit up-counter with a programmable 20-bit prescaler
- Alarm function
- Interrupt and wake-up event

The real time clock is an independent timer which provides a set of continuously running counters which can be used with suitable software to provide a clock calendar function, and provides an alarm interrupt and an expected interrupt. The RTC features a 32-bit programmable counter for long-term measurement using the compare register to generate an alarm. A 20-bit prescaler is used for the time base clock and is by default configured to generate a time base of 1 second from a clock at 32.768 KHz from external crystal oscillator.

3.12. Inter-integrated circuit (I2C)

- Up to two I2C bus interfaces can support both master and slave mode with a frequency up to 1 MHz (Fast mode plus)
- Provide arbitration function, optional PEC (packet error checking) generation and checking
- Supports 7-bit and 10-bit addressing mode and general call addressing mode

The I2C interface is an internal circuit allowing communication with an external I2C interface which is an industry standard two line serial interface used for connection to external hardware. These two serial lines are known as a serial data line (SDA) and a serial clock line (SCL). The I2C module provides several data transfer rates: up to 100 KHz of standard mode, up to 400 KHz of the fast mode and up to 1 MHz of the fast mode plus. The I2C module also has an arbitration detect function to prevent the situation where more than one master attempts to transmit data to the I2C bus at the same time. A CRC-8 calculator is also provided in I2C interface to perform packet error checking for I2C data.

3.13. Serial peripheral interface (SPI)

- Up to three SPI interfaces with a frequency of up to 30 MHz
- Support both master and slave mode
- Hardware CRC calculation and transmit automatic CRC error checking
- Quad-SPI configuration available in master mode (only in SPI0)
- SPI TI mode and NSS pulse mode supported



The SPI interface uses 4 pins, among which are the serial data input and output lines (MISO & MOSI), the clock line (SCK) and the slave select line (NSS). Both SPIs can be served by the DMA controller. The SPI interface may be used for a variety of purposes, including simplex synchronous transfers on two lines with a possible bidirectional data line or reliable communication using CRC checking.

3.14. Universal synchronous asynchronous receiver transmitter (USART)

- Up to three USARTs and two UARTs with operating frequency up to 7.5MBits/s
- Supports both asynchronous and clocked synchronous serial communication modes
- IrDA SIR encoder and decoder support
- LIN break generation and detection
- USARTs support ISO 7816-3 compliant smart card interface

The USART (USART0, USART1 and USART2) and UART (UART3 & UART4) are used to translate data between parallel and serial interfaces, provides a flexible full duplex data exchange using synchronous or asynchronous transfer. It is also commonly used for RS-232 standard communication. The USART/UART includes a programmable baud rate generator which is capable of dividing the system clock to produce a dedicated clock for the USART transmitter and receiver. The USART/UART also supports DMA function for high speed data communication except UART4.

3.15. Inter-IC sound (I2S)

- Two I2S bus interfaces with sampling frequency from 8 KHz to 192 KHz
- Support either master or slave mode

The Inter-IC sound (I2S) bus provides a standard communication interface for digital audio applications by 3-wire serial lines. GD32E103xx contain two I2S-bus interfaces that can be operated with 16/32 bit resolution in master or slave mode, pin multiplexed with SPI1 and SPI2. The audio sampling frequency from 8 KHz to 192 KHz is supported.

3.16. Universal serial bus full-speed interface (USBFS)

- One full-speed USB Interface with frequency up to 12 Mbit/s
- Internal 48 MHz oscillator support crystal-less operation
- Internal main PLL for USB CLK compliantly

The Universal Serial Bus (USB) is a 4-wire bus with 4 bidirectional endpoints. The device controller enables 12 Mbit/s data exchange with integrated transceivers. Transaction formatting is performed by the hardware, including CRC generation and checking. It supports



device modes. The status of a completed USB transfer or error condition is indicated by status registers. An interrupt is also generated if enabled. The required precise 48 MHz clock which can be generated from the internal main PLL (the clock source must use an HXTAL crystal oscillator) or by the internal 48 MHz oscillator in automatic trimming mode that allows crystalless operation.

3.17. Controller area network (CAN)

- Two CAN interface supports the CAN protocols version 2.0A, 2.0B, ISO11891-1:2015 and BOSCH CAN FD specification with communication frequency up to 1 Mbit/s of classic frames and 6 Mbit/s of FD frames
- Internal main PLL for CAN CLK compliantly

Controller area network (CAN) is a method for enabling serial communication in field bus. The CAN protocol has been used extensively in industrial automation and automotive applications. It can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. Each CAN has three mailboxes for transmission and two FIFOs of three message deep for reception. It also provides 28 scalable/configurable identifier filter banks for selecting the incoming messages needed and discarding the others.

3.18. External memory controller (EXMC)

- Supported external memory: SRAM, PSRAM, ROM and NOR-Flash
- Up to 16-bit data bus
- Support to interface with Motorola 6800 and Intel 8080 type LCD directly

External memory controller (EXMC) is an abbreviation of external memory controller. It is divided in to several sub-banks for external device support, each sub-bank has its own chip selection signal but at one time, only one bank can be accessed. The EXMC support code execution from external memory. The EXMC also can be configured to interface with the most common LCD module of Motorola 6800 and Intel 8080 series and reduce the system cost and complexity.

3.19. Debug mode

■ Serial wire JTAG debug port (SWJ-DP)

The ARM®SWJ-DP Interface is embedded and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target.

3.20. Package and operation temperature

■ LQFP100 (GD32E103Vx), LQFP64 (GD32E103Rx) and LQFP48 (GD32E103Cx) QFN36



(GD32E103Tx)

■ Operation temperature range: -40°C to +85°C (industrial level)



4. Electrical characteristics

4.1. Absolute maximum ratings

The maximum ratings are the limits to which the device can be subjected without permanently damaging the device. Note that the device is not guaranteed to operate properly at the maximum ratings. Exposure to the absolute maximum rating conditions for extended periods may affect device reliability.

Table 4-1. Absolute maximum ratings(1)(4)

Symbol	Parameter	Min	Max	Unit
V_{DD}	External voltage range ⁽²⁾	V _{SS} - 0.3	V _{SS} + 3.6	V
V_{DDA}	External analog supply voltage	V _{SSA} - 0.3	V _{SSA} + 3.6	V
Vват	External battery supply voltage	Vss - 0.3	Vss + 3.6	V
V _{IN}	Input voltage on 5V tolerant pin(3)	Vss - 0.3	V _{DD} +3.6	V
VIN	Input voltage on other I/O	Vss - 0.3	3.6	V
AVDDX	Variations between different V _{DD} power pins	_	50	mV
Vssx -Vss	Variations between different ground pins	_	50	mV
lio	Maximum current for GPIO pins	_	±25	mA
TA	Operating temperature range	-40	+85	°C
T _{STG}	Storage temperature range	-55	+150	°C
TJ	Maximum junction temperature	_	125	°C

^{(1).} Guaranteed by design, not tested in production.

4.2. Operating conditions characteristics

Table 4-2. DC operating conditions

Symbol	Parameter	Conditions	Min ⁽¹⁾	Тур	Max ⁽¹⁾	Unit
V_{DD}	Supply voltage	_	1.71	3.3	3.6	V
V _{DDA}	Analog supply voltage ADC not used	1.71 3.3 3.6	V			
VDDA	Analog supply voltage ADC used	_	2.4	3.3	3.6	V
VBAT	Battery supply voltage	_	1.71	_	3.6	V

^{(1).} Based on characterization, not tested in production.

Table 4-3. Clock frequency

	. ,				
Symbol	Parameter	Conditions	Min	Max	Unit
f _{HCLK}	AHB clock frequency	_	_	120	MHz

^{(2).} All main power and ground pins should be connected to an external power source within the allowable range.

^{(3).} V_{IN} maximum value cannot exceed 6.5V.

^{(4).} It is recommended that V_{DD} and V_{DDA} are powered by the same source. The maximum difference between V_{DD} and V_{DDA} does not exceed 300 mV during power-up and operation.



f _{APB1}	APB1 clock frequency		60	MHz
f _{APB2}	APB2 clock frequency	_	120	MHz

Table 4-4. Operating conditions at Power up/ Power down

Symbol	Parameter	Conditions	Min	Max	Unit
t _{VDD} ⁽¹⁾	V _{DD} rise time rate		0	8	
(VDD(**)	V _{DD} fall time rate	_	20	8	µs/V

^{(1).} Based on characterization, not tested in production.

Table 4-5. Start-up timings of Operating conditions

Symbol	Parameter	Conditions	Тур	Unit
± (1)(2)(3)	Ctart up time	Clock source from HXTAL	468	
t _{start-up} (1)(2)(3)	Start-up time	Clock source from IRC8M	86.8	μs

- (1). Based on characterization, not tested in production.
- (2). After power-up, the start-up time is the time between the rising edge of NRST high and the main function.
- (3). PLL is off.

Table 4-6. Power saving mode wakeup timings characteristics(1)(2)

Symbol	Parameter	Тур	Unit
tsleep	Wakeup from Sleep mode	4.3	
4-	Wakeup from Deep-sleep mode (LDO On)	18.0	
tDeep-sleep	Wakeup from Deep-sleep mode (LDO in low power mode)	18.0	μs
tStandby	Wakeup from Standby mode	82.0	

- (1). Based on characterization, not tested in production.
- (2). The wakeup time is measured from the wakeup event to the point at which the application code reads the first instruction under the below conditions: $V_{DD} = V_{DDA} = 3.3 \text{ V}$, IRC8M = System clock = 8 MHz.

4.3. Power consumption

The power measurements specified in the tables represent that code with data executing from on-chip Flash with the following specifications.

Table 4-7. Power consumption characteristics(1)(2)(3)(4)(5)(6)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz, System clock=120 MHz, All peripherals	_	28.1		mA
		enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{ HXTAL} = 25 \text{ MHz},$				
		System clock = 120 MHz, All peripherals		16.3	_	mA
IDD+IDDA	Supply current	disabled				
	(Run mode)	$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{ HXTAL} = 25 \text{ MHz},$				
		System clock = 108 MHz, All peripherals	_	24.6	_	mA
		enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{ HXTAL} = 25 \text{ MHz},$				
		System clock = 108 MHz, All peripherals	_	14.7	_	mΑ
		disabled				



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
-		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$		- 71		
		System clock = 96 MHz, All peripherals	_	22.3	_	mA
		enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System clock = 96 MHz, All peripherals	_	13.6	_	mA
		disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System clock = 72 MHz, All peripherals	_	17.2		mA
		enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System clock = 72 MHz, All peripherals	_	10.8		mA
		disabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25MHz,				
		System clock = 48 MHz, All peripherals	_	12.3		mA
		enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System clock = 48 MHz, All peripherals	_	8.1		mA
		disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System clock = 36 MHz, All peripherals	_	9.8	_	mA
		enabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System clock = 36 MHz, All peripherals	_	6.7	_	mA
		disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System clock = 24 MHz, All peripherals	_	7.4		mA
		enabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System clock = 24 MHz, All peripherals	_	5.3	_	mA
		disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System clock = 16 MHz, All peripherals	_	5.7	_	mA
		enabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System clock = 16 MHz, All peripherals	_	4.4		mA
		disabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System clock = 8 MHz, All peripherals	—	4.1	_	mA
		enabled	L	L		
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System clock = 8 MHz, All peripherals	—	3.4	_	mA
		disabled				



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 4 \text{ MHz,}$				
		System clock = 4MHz, All peripherals	_	1.4	_	mA
		enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 4 \text{ MHz,}$				
		System clock = 4MHz, All peripherals	_	1.0	_	mA
		disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 2 \text{ MHz,}$				
		System clock = 2 MHz, All peripherals	_	0.9	_	mA
		enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 2 \text{ MHz,}$				
		System Clock = 2 MHz, All peripherals	_	0.7	_	mA
		disabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System Clock = 120 MHz, CPU clock off, All	_	20.5	_	mA
		peripherals enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System Clock = 120 MHz, CPU clock off, All	_	6.9	_	mA
		peripherals disabled				
		$V_{DD} = V_{DDA} = 3.3V$, HXTAL = 25 MHz,				
		System Clock = 108 MHz, CPU clock off, All	_	18.6	_	mA
		peripherals enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System Clock = 108 MHz, CPU clock off, All	_	6.4	_	mA
		peripherals disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System Clock = 96 MHz, CPU clock off, All	_	16.5	_	mA
	Supply current	peripherals enabled				
	(Sleep mode)	V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System Clock = 96 MHz, CPU clock off, All	_	5.8	_	mA
		peripherals disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System Clock = 72 MHz, CPU clock off, All	_	13	_	mΑ
		peripherals enabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System Clock = 72 MHz, CPU clock off, All	_	5	_	mA
		peripherals disabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System Clock = 48 MHz, CPU clock off, All	_	9.5	_	mA
		peripherals enabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System Clock = 48 MHz, CPU clock off, All	_	4.1	_	mA
		peripherals disabled				



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System Clock = 36 MHz, CPU clock off, All	_	7.7	_	mA
		peripherals enabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System Clock = 36 MHz, CPU clock off, All	_	3.7	_	mA
		peripherals disabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System Clock = 24 MHz, CPU clock off, All	_	5.9	_	mA
		peripherals enabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System Clock = 24 MHz, CPU clock off, All	_	3.3	_	mA
		peripherals disabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System Clock = 16 MHz, CPU clock off, All	_	4.8	_	mA
		peripherals enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System Clock = 16 MHz, CPU clock off, All	_	3	_	mA
		peripherals disabled				
		V _{DD} = V _{DDA} = 3.3 V, HXTAL = 25 MHz,				
		System Clock = 8 MHz, CPU clock off, All	_	3.6	_	mA
		peripherals enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System Clock = 8 MHz, CPU clock off, All	_	2.7	_	mA
		peripherals disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 4 \text{ MHz,}$				
		System Clock = 4 MHz, CPU clock off, All	_	1.1	_	mA
		peripherals enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 4 \text{ MHz,}$				
		System Clock = 4 MHz, CPU clock off, All	_	0.6	_	mA
		peripherals disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 2 \text{ MHz,}$				
		System Clock = 2 MHz, CPU clock off, All	_	0.8	_	mA
		peripherals enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 2 \text{ MHz,}$				
		System Clock = 2 MHz, CPU clock off, All	_	0.6	_	mA
		peripherals disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, LDO in run mode,}$				
		IRC40K off, RTC off, All GPIOs analog	_	60.2	220	μA
	Supply current	mode				F=-/ •
	(Deep-Sleep	$V_{DD} = V_{DDA} = 3.3 \text{ V, LDO in low power}$				
	mode)	mode, IRC40K off, RTC off, All GPIOs	_	50.2	220	μA
		analog mode				,
1		l analog mode	<u> </u>			<u> </u>



_			OD32L			4140	
	Symbol	Parameter	Conditions	Min	Тур	Max	Unit
			$\label{eq:VDD} V_{DD} = V_{DDA} = 3.3 \ V, \ LXTAL \ off, \ IRC40K \ on,$ RTC on	_	2.1	11	μΑ
		Supply current (Standby mode)	$\label{eq:VDD} V_{DD} = V_{DDA} = 3.3 \ V, \ \text{LXTAL off, IRC40K on,}$ RTC off	l	2.0	11	μΑ
			$V_{\text{DD}} = V_{\text{DDA}} = 3.3 \text{ V, LXTAL off, IRC40K off,}$ RTC off		1.5	11	μA
			V_{DD} off, V_{DDA} off, V_{BAT} = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL High driving	l	1.6	l	μΑ
			V_{DD} off, V_{DDA} off, V_{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL High driving	ı	1.4	ı	μΑ
			V_{DD} off, V_{DDA} off, V_{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL High driving		1.3	_	μΑ
			V_{DD} off, V_{DDA} off, V_{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL High driving	_	1.2	_	μΑ
			V _{DD} off, V _{DDA} off, V _{BAT} = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL Medium High driving	_	1.3	_	μΑ
	ı	Battery supply	V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Medium High driving	_	1.1	_	μΑ
	Іват	current (Backup mode)	V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Medium High driving		1.0		μΑ
			V_{DD} off, V_{DDA} off, V_{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Medium High driving		0.9		μΑ
			V_{DD} off, V_{DDA} off, V_{BAT} = 3.6 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving	_	1.0	_	μΑ
			V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving	_	0.9	_	μΑ
			V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving	_	0.7	_	μΑ
			V_{DD} off, V_{DDA} off, V_{BAT} = 1.71 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving	_	0.6	_	μΑ



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V_{DD} off, V_{DDA} off, $V_{BAT} = 3.6 \text{ V}$, LXTAL on				
		with external crystal, RTC on, LXTAL Low	_	0.9	_	μΑ
		driving				
		V _{DD} off, V _{DDA} off, V _{BAT} = 3.3 V, LXTAL on				
		with external crystal, RTC on, LXTAL Low	_	8.0	_	μΑ
		driving				
		V _{DD} off, V _{DDA} off, V _{BAT} = 2.5 V, LXTAL on				
		with external crystal, RTC on, LXTAL Low	_	0.6	_	μΑ
		driving				
		V _{DD} off, V _{DDA} off, V _{BAT} = 1.71 V, LXTAL on				
		with external crystal, RTC on, LXTAL Low		0.5	_	μΑ
		driving				

- (1). Based on characterization, not tested in production.
- (2). Unless otherwise specified, all values given for TA = 25 $\,^{\circ}$ C and test result is mean value.
- (3). When System Clock is less than 4 MHz, an external source is used, and the HXTAL bypass function is needed, no PLL.
- (4). When System Clock is greater than 8 MHz, a crystal 25MHz is used, and the HXTAL bypass function is closed, using PLL.
- (5). When analog peripheral blocks such as ADCs, DACs, HXTAL, LXTAL, IRC8M, or IRC40K are ON, an additional power consumption should be considered.
- (6). The power measurements specified in the tables represent that code with data executing from on-chip Flash with the following specifications.

Table 4-8. Peripheral current consumption characteristics⁽¹⁾

	Peripherials ⁽⁴⁾	Typical consumption at 25 ℃ (TYP)	Unit
	DAC ⁽²⁾	0.44	
	PMU	0.18	
	ВКРІ	0.38	
	CAN1	0.3	
	CAN0	0.32	
	I2C1	0.77	
	I2C0	0.77	
	UART4	0.78	
	UART3	0.78	
APB1	USART2	0.78	mA
	USART1	0.78	
	SPI2	0.72	
	SPI1	0.78	
	WWDGT	0.03	
	TIMER13	0.32	
	TIMER12	0.3	
	TIMER11	0.31	
	TIMER6	0.05	
	TIMER5	0.04	



		0 - 0 - 1 - 0 - 0 - 0 - 0 - 0 - 0 - 0 -	
	Peripherials ⁽⁴⁾	Typical consumption at 25 ℃ (TYP)	Unit
	TIMER4	0.38	
	TIMER3	0.37	
	TIMER2	0.36	
	TIMER1	0.37	
ADDAPB1	СТС	0.68	
	TIMER10	0.56	
	TIMER9	0.58	
	TIMER8	0.6	
	USART0	0.52	
	TIMER7	0.87	
	SPI0	0.09	
	TIMER0	0.65	
APB2	ADC1 ⁽³⁾	1.36	
	ADC0 ⁽³⁾	1.35	
	GPIOE	0.18	
	GPIOD	0.19	
	GPIOC	0.2	
	GPIOB	0.18	
	GPIOA	0.19	
	GPIOF	0.04	
	USBFS	1.48	
	EXMC	0.29	
AHB	CRC	0.03	
	DMA1	0.31	
	DMA0	0.39	

^{(1).} Based on characterization, not tested in production.

4.4. EMC characteristics

EMS (electromagnetic susceptibility) includes ESD (Electrostatic discharge, positive and negative) and FTB (Burst of Fast Transient voltage, positive and negative) testing result is given in the <u>Table 4-9. EMS characteristics</u>, based on the EMS levels and classes compliant with IEC 61000 series standard.

Table 4-9. EMS characteristics(1)

Symbol	Parameter	Conditions	Level/Class
\/	Voltage applied to all device pins to	$V_{DD} = 3.3 \text{ V}, T_A = +25 ^{\circ}\text{C},$	3A
V _{ESD}	induce a functional disturbance	LQFP100, f _{HCLK} = 120 MHz	3A

^{(2).} DEN0 and DEN1 bits in the DAC_CTL register are set to 1, and the converted value set to 0x800.

^{(3).} System clock = f_{HCLK} = 72 Mhz, f_{APB1} = $f_{HCLK}/2$, f_{APB2} = f_{HCLK} , f_{ADCCLK} = $f_{APB2}/2$, ADCON bit is set to 1.

^{(4).} If there is no other description, then HXTAL = 25Mhz, system clock = f_{HCLK} = 120Mhz, f_{APB1} = f_{HCLK} /2, f_{APB2} = f_{HCLK} .



		conforms to IEC 61000-4-2	
	Fast transient voltage burst applied to	$V_{DD}= 3.3 \text{ V}, T_{A}=+25 ^{\circ}\text{C},$	
V_{FTB}	induce a functional disturbance through	LQFP100, f _{HCLK} = 120 MHz	4A
	100 pF on V_{DD} and V_{SS} pins	conforms to IEC 61000-4-4	

^{(1).} Based on characterization, not tested in production.

4.5. Power supply supervisor characteristics

Table 4-10. Power supply supervisor characteristics(1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		LVDT<2:0> = 000(rising edge)	_	2.07	_	
		LVDT<2:0> = 000(falling edge)	_	1.97		
		LVDT<2:0> = 001(rising edge)	_	2.2		
	LVDT<2:0> = 001(falling edge)		2.1			
		LVDT<2:0> = 010(rising edge)		2.34		
		LVDT<2:0> = 010(falling edge)	_	2.24		
		LVDT<2:0> = 011(rising edge)	_	2.47	_	
V	Low voltage	LVDT<2:0> = 011(falling edge)	_	2.37		\ /
V _{LVD}	Detector Threshold	LVDT<2:0> = 100(rising edge)	_	2.61		V
		LVDT<2:0> = 100(falling edge)	_	2.51		
		LVDT<2:0> = 101(rising edge)	_	2.74	_	
		LVDT<2:0> = 101(falling edge)	_	2.64	_	
		LVDT<2:0> = 110(rising edge)	_	2.88	_	
		LVDT<2:0> = 110(falling edge)	_	2.78	_	
		LVDT<2:0> = 111(rising edge)	_	3.01	_	
		LVDT<2:0> = 111(falling edge)	_	2.91	_	
V _{LVDhyst}	LVD hystersis	_	_	100	_	mV
V _{POR}	Power on reset threshold		_	1.66	_	V
V _{PDR}	Power down reset		_	1.62	_	V
VPDPhyet		_		0.04		V
trsttemp	Reset temporization		_	2.5	_	ms
V _{PDRhyst}	threshold PDR hysteresis	_	_ 	0.04	_	V

^{(1).} Based on characterization, not tested in production.



4.6. Electrical sensitivity

The device is strained in order to determine its performance in terms of electrical sensitivity. Electrostatic discharges (ESD) are applied directly to the pins of the sample. Static latch-up (LU) test is based on the two measurement methods.

Table 4-11. ESD characteristics(1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V	Electrostatic discharge	T _A = 25 °C; JESD22-			5000	V
VESD(HBM)	voltage (human body model)	A114			3000	V
V	Electrostatic discharge	T _A = 25 °C;			900	V
VESD(CDM)	voltage (charge device model)	JESD22-C101			800	V

^{(1).} Based on characterization, not tested in production.

Table 4-12. Static latch-up characteristics(1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
LU	I-test	T _A = 25 °C; JESD78		_	±200	mA
	V _{supply} over voltage	TA = 25 C, JESD76	_	_	5.4	V

^{(1).} Based on characterization, not tested in production.

4.7. External clock characteristics

Table 4-13. High speed external clock (HXTAL) generated from a crystal/ceramic characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{HXTAL} ⁽¹⁾	Crystal or ceramic frequency	1.71 V ≤ V _{DD} ≤ 3.6 V	4	8	32	MHz
R _F ⁽²⁾	Feedback resistor	V _{DD} = 3.3 V	_	400	_	$\mathbf{k} \Omega$
Снхтац ^{(2) (3)}	Recommended matching capacitance on OSCIN and OSCOUT	_		20	30	pF
Ducy _(HXTAL) ⁽²⁾	Crystal or ceramic duty cycle	_	30	50	70	%
I _{DD(HXTAL)} ⁽¹⁾	Crystal or ceramic operating current	V _{DD} = 3.3 V, T _A = 25 °C	_	1.1	_	mA
tsuhxtal ⁽¹⁾	Crystal or ceramic startup time	V _{DD} = 3.3 V, T _A = 25 °C	_	1.8	_	ms

^{(1).} Based on characterization, not tested in production.

Table 4-14. High speed external clock characteristics (HXTAL in bypass mode)

Symbo	Parameter	Conditions	Min	Тур	Max	Unit
f _{HXTAL_ext}	External clock source or oscillator	$V_{DD} = 3.3 \text{ V}$	1	_	50	MHz

^{(2).} Guaranteed by design, not tested in production.

^{(3).} C_{HXTAL1} = C_{HXTAL2} = 2*(C_{LOAD} - C_S), For C_{HXTAL1} and C_{HXTAL2}, it is recommended matching capacitance on OSCIN and OSCOUT. For C_{LOAD}, it is crystal/ceramic load capacitance, provided by the crystal or ceramic manufacturer. For C_S, it is PCB and MCU pin stray capacitance.



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	frequency					
V _{HXTALH} ⁽²⁾	OSCIN input pin high level voltage	V _{DD} = 3.3 V	$0.7V_{DD}$		V_{DD}	V
V _{HXTALL} ⁽²⁾	OSCIN input pin low level voltage	VDD = 3.3 V	V_{SS}	_	$0.3V_{DD}$	V
t _{H/L(HXTAL)} (2)	OSCIN high or low time		5			ns
t _{R/F(HXTAL)} (2)	OSCIN rise or fall time	_	_	_	10	ns
C _{IN} ⁽¹⁾	OSCIN input capacitance			5	_	pF
Ducy _(HXTAL) (2)	Duty cycle	_	40	_	60	%

^{(1).} Based on characterization, not tested in production.

Table 4-15. Low speed external clock (LXTAL) generated from a crystal/ceramic characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{LXTAL} ⁽¹⁾	Crystal or ceramic frequency			32.768		kHz
C _{LXTAL} ⁽²⁾ (3)	Recommended matching capacitance on OSC32IN and OSC32OUT	_	_	10	_	pF
Ducy _(LXTAL) (2)	Crystal or ceramic duty cycle	_	30	_	70	%
		LXTALDRI[1:0] = 00		0.7		
(1)	Crystal or ceramic operating	LXTALDRI[1:0] = 01		0.8		
IDDLXTAL (1)	current	LXTALDRI[1:0] = 10		1.1	_	μA
		LXTALDRI[1:0] = 11		1.4		
tsulxtal ⁽¹⁾ (4)	Crystal or ceramic startup time	_	_	1.8	_	s

^{(1).} Based on characterization, not tested in production.

Table 4-16.Low speed external user clock characteristics (LXTAL in bypass mode)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
fLXTAL_ext	External clock source or oscillator frequency	_	_	32.768	1000	kHz
V _{LXTALH} ⁽¹⁾	OSC32IN input pin high level voltage	_	0.7V _{DD}	_	V _{DD}	.,,
VLXTALL (1)	OSC32IN input pin low level voltage	_	Vss		0.3V _{DD}	V
t _{H/L(LXTAL)} (1)	OSC32IN high or low time	_	450	_	_	
t _{R/F(LXTAL)} (1)	OSC32IN rise or fall time	_	_	_	50	ns
C _{IN} ⁽¹⁾	OSC32IN input capacitance	_	_	5	_	pF

^{(2).} Guaranteed by design, not tested in production.

^{(2).} Guaranteed by design, not tested in production.

^{(3).} $C_{LXTAL1} = C_{LXTAL2} = 2*(C_{LOAD} - C_S)$, For C_{LXTAL1} and C_{LXTAL2} , it is recommended matching capacitance on OSC32IN and OSC32OUT. For C_{LOAD} , it is crystal/ceramic load capacitance, provided by the crystal or ceramic manufacturer. For C_S , it is PCB and MCU pin stray capacitance.

^{(4).} tsulxtal is the startup time measured from the moment it is enabled (by software) to the 32.768 kHz oscillator stabilization flags is SET. This value varies significantly with the crystal manufacturer.



Ducy(LXIAL) \ \ \ Duty cycle \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \		70	50	30	_	Duty cycle	Ducy _(LXTAL) (1)	
--	--	----	----	----	---	------------	-----------------------------	--

^{(1).} Guaranteed by design, not tested in production.

4.8. Internal clock characteristics

Table 4-17. High speed internal clock (IRC8M) characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{IRC8M}	High Speed Internal Oscillator (IRC8M) frequency	$V_{DD} = V_{DDA} = 3.3 \text{ V}$	_	8	l	MHz
	IDCOM cocillator Fraguency	$V_{DD} = V_{DDA} = 3.3 \text{ V}, T_A = -40 \text{ °C}$ ~+105 °C ⁽¹⁾	-2.5		+2.5	%
ACC _{IRC8M}	IRC8M oscillator Frequency accuracy, Factory-trimmed	$V_{DD} = V_{DDA} = 3.3 \text{ V, } T_A = 0 \text{ °C } \sim$ +85 °C ⁽¹⁾	-1.8		+1.8	%
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, T_A = 25 ^{\circ}\text{C}$	-1.0		+1.0	%
	IRC8M oscillator Frequency accuracy, User trimming step ⁽¹⁾	Ι	_	0.3	ı	%
Ducy _{IRC8M} (2)	IRC8M oscillator duty cycle	$V_{DD} = V_{DDA} = 3.3 \text{ V, fircsm} = 8$ MHz	45	50	55	%
IDDAIRC8M ⁽¹⁾	IRC8M oscillator operating current	$V_{DD} = V_{DDA} = 3.3 \text{ V, fircsm} = 8$ MHz	_	110	_	μΑ
tsuirc8M ⁽¹⁾	IRC8M oscillator startup time	$V_{DD} = V_{DDA} = 3.3 \text{ V, fircsm} = 8$ MHz		2	_	μs

^{(1).} Based on characterization, not tested in production.

Table 4-18. Low speed internal clock (IRC40K) characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
firc40K ⁽¹⁾	Low Speed Internal oscillator (IRC40K) frequency	$V_{DD} = V_{DDA} = 3.3 \text{ V},$ $T_A = -40 \text{ °C} \sim +85 \text{ °C}$	28	40	60	KHz
IDDAIRC40K ⁽²⁾	IRC40K oscillator operating current	V _{DD} = V _{DDA} = 3.3 V, T _A = 25 °C	_	0.42	_	μA
tsuirc40K ⁽²⁾	IRC40K oscillator startup time	V _{DD} = V _{DDA} = 3.3 V, T _A = 25 °C	_	110	_	μs

^{(1).} Guaranteed by design, not tested in production.

Table 4-19. High speed internal clock (IRC48M) characteristics

	0 1	, ,				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	High Speed Internal					
f _{IRC48M}	Oscillator (IRC48M)	$V_{DD} = V_{DDA} = 3.3 \text{ V}$	_	48	_	MHz
	frequency					
ACCIRC48M	IRC48M oscillator	V _{DD} = V _{DDA} = 3.3 V, T _A = -40 °C	-4.0	_	5.0	%

^{(2).} Guaranteed by design, not tested in production.

^{(2).} Based on characterization, not tested in production.



	Frequency accuracy,	~+105 °C ⁽¹⁾				
	Factory-trimmed	$V_{DD} = V_{DDA} = 3.3 \text{ V, } T_A = 0 \text{ °C } \sim$ +85 °C ⁽¹⁾	-3.0		3.0	%
		V _{DD} = V _{DDA} = 3.3 V, T _A = 25°C	-2.0	_	2.0	%
	IRC48M oscillator					
	Frequency accuracy, User	_	_	0.1	_	%
	trimming step ⁽¹⁾					
Ducy _{IRC48M} ⁽²⁾	IRC48M oscillator duty	V _{DD} = V _{DDA} = 3.3 V, f _{IRC48M} = 48	45	50	55	%
DGCYIRC48M	cycle	MHz	P	30	3	70
I _{DDIRC48M} ⁽¹⁾	IRC48M oscillator	$V_{DD} = V_{DDA} = 3.3V$, $f_{IRC48M} = 48$		270		μA
IDDIRC48M\''	operating current	MHz		270		μΑ
tsuirc48M ⁽¹⁾	IRC48M oscillator startup	V _{DD} = V _{DDA} = 3.3 V, f _{IRC48M} = 48		2.5	·	
ISUIRC48M(1)	time	MHz	_	2.5	_	μs

^{(1).} Based on characterization, not tested in production.

4.9. PLL characteristics

Table 4-20. PLL characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{PLLIN} ⁽¹⁾	PLL input clock frequency	_	1	8	25	MHz
f _{PLLOUT}	PLL output clock frequency	_	16	_	120	MHz
f _{VCO}	VCO output frequency	_	32	_	240	MHz
tLOCK ⁽²⁾	PLL lock time	_	_	_	300	μs
I _{DD} ⁽¹⁾	Current consumption on	VCO freq = 240 MHz		520		
IDD(1)	V_{DD}	VOO 1164 – 240 WI 12		520		μΑ
I _{DDA} ⁽¹⁾	Current consumption on	VCO freq = 240 MHz		350		
IDDA\ /	V _{DDA}	VCO 11eq = 240 W112		330		μΑ
	Cycle to cycle Jitter			46		
littora (1)(3)	(rms)	System clock		40	_	nc
Jitter _{PLL} ⁽¹⁾⁽³⁾	Cycle to cycle Jitter	System Clock		463		ps
	(peak to peak)			403		

^{(1).} Based on characterization, not tested in production.

Table 4-21. PLL1/2 characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{PLLIN} ⁽¹⁾	PLL input clock frequency	_	1	8	25	MHz
f PLLOUT	PLL output clock frequency	_	16	_	120	MHz
fvco	VCO output frequency	_	32	_	240	MHz
tLOCK ⁽²⁾	PLL lock time	_	_	_	300	μs
I (1)	Current consumption on	V00 (040 MH		500		
I _{DD} ⁽¹⁾	V_{DD}	VCO freq = 240 MHz	_	520	_	μΑ

^{(2).} Guaranteed by design, not tested in production.

^{(2).} Guaranteed by design, not tested in production.

^{(3).} Value given with main PLL running.

I _{DDA} ⁽¹⁾	Current consumption on V _{DDA}	VCO freq = 240 MHz	_	320		μА
Jitter _{PLL} ⁽¹⁾⁽³⁾	Cycle to cycle Jitter (rms)	Cuetare electr	_	46	_	
	Cycle to cycle Jitter (peak to peak)	System clock	_	463	_	ps

- (1). Based on characterization, not tested in production.
- (2). Guaranteed by design, not tested in production.
- (3). Value given with main PLL running

4.10. Memory characteristics

Table 4-22. Flash memory characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	Number of guaranteed					
PEcyc ⁽¹⁾	program /erase cycles	$T_A = -40 ^{\circ}\text{C} \sim +85 ^{\circ}\text{C}$	100	_	_	kcycles
	before failure(Endurance)					
t _{RET} ⁽¹⁾	Data retention time	10k cycles at T _A = 85 °C	10	_	_	years
t _{PROG} (2)	Word ⁽³⁾ programming time	T _A = -40 °C ~ +85°C	37		44	μs
terase(2)	Page erase time	T _A = -40 °C ~ +85°C	3.2		4	ms
t _{MERASE} (2)	Mass erase time	T _A = -40 °C ~ +85°C	8		10	ms

- (1). Based on characterization, not tested in production.
- (2). Guaranteed by design, not tested in production.
- (3). Word is 32bits or 64bits depend on PGW bit in FMC_WS register.

4.11. NRST pin characteristics

Table 4-23. NRST pin characteristics

	<u>-</u>						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
V _{IL(NRST)} ⁽¹⁾	NRST Input low level voltage		-0.5	_	0.66	.,	
V _{IH(NRST)} ⁽¹⁾	NRST Input high level voltage	$V_{DD} = V_{DDA} = 1.8 \text{ V}$	1.1	_	V _{DD} + 0.5	V	
V _{hyst} ⁽¹⁾	Schmidt trigger Voltage hysteresis		_	270		mV	
V _{IL(NRST)} ⁽¹⁾	NRST Input low level voltage		-0.5		1.44	V	
V _{IH(NRST)} ⁽¹⁾	NRST Input high level voltage	$V_{DD} = V_{DDA} = 3.3 \text{ V}$	1.9		V _{DD} + 0.5	V	
V _{hyst} ⁽¹⁾	Schmidt trigger Voltage hysteresis		_	350	_	mV	
V _{IL(NRST)} ⁽¹⁾	NRST Input low level voltage		-0.5		1.5	.,	
V _{IH(NRST)} ⁽¹⁾	NRST Input high level voltage	$V_{DD} = V_{DDA} = 3.6 \text{ V}$	2.05	_	V _{DD} + 0.5	V	
V _{hyst} ⁽¹⁾	Schmidt trigger Voltage hysteresis		_	360	_	mV	
R _{pu} ⁽²⁾	Pull-up equivalent resistor	_		40	_	kΩ	

- (1). Based on characterization, not tested in production.
- (2). Guaranteed by design, not tested in production.



4.12. **GPIO** characteristics

Table 4-24. I/O port DC characteristics(1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _{DD} = 1.8 V	_	_	0.8	
	Standard IO Low level input	V _{DD} = 2.5 V	_	_	1.12	
	voltage	V _{DD} = 3.3 V	_	_	1.47	V
\ <i>/</i>		V _{DD} = 3.6 V	_	_	1.60	
V_{IL}		V _{DD} = 1.8 V	_	_	0.81	
	5V-tolerant IO Low level	$V_{DD} = 2.5 \text{ V}$	_	_	1.12	\ ,
	input voltage	V _{DD} = 3.3 V	_	_	1.47	V
		V _{DD} = 3.6 V	_	_	1.60	
		V _{DD} = 1.8 V	1.28	_	_	
	Standard IO High level	$V_{DD} = 2.5 \text{ V}$	1.70	_	_	\ ,
	input voltage	V _{DD} = 3.3 V	1.94	_	_	V
		V _{DD} = 3.6 V	2.05	_	_	
V _{IH}		V _{DD} = 1.8 V	1.3	_	_	
	5V-tolerant IO High level	V _{DD} = 2.5 V	1.70	_	_	\ ,
	input voltage	V _{DD} = 3.3 V	1.94	_	_	V
		V _{DD} = 3.6 V	2.05	_	_	
		V _{DD} = 1.8 V	_	_	0.32	V
.,	Low level output voltage	V _{DD} = 2.5 V	_	_	0.24	
V_{OL}	$(I_{IO} = +8 \text{ mA})$	V _{DD} = 3.3 V	_	_	0.11	
		V _{DD} = 3.6 V	_	_	0.11	
		V _{DD} = 1.8 V	_	_	0.53	
	Low level output voltage	V _{DD} = 2.5 V	_	_	0.60	.,
V_{OL}	(I _{IO} = +20 mA)	V _{DD} = 3.3 V	_	_	0.28	V
		V _{DD} = 3.6 V	_	_	0.27	
		V _{DD} = 1.8 V	1.49	_	_	
.,	High level output voltage	V _{DD} = 2.5 V	2.27	_	_	,,
V_{OH}	$(I_{IO} = +8 \text{ mA})$	V _{DD} = 3.3 V	3.14	_	_	V
		V _{DD} = 3.6 V	3.45	_	_	
		V _{DD} = 1.8 V	1.25	_	_	
.,	High level output voltage	V _{DD} = 2.5 V	1.89	_	_	,,
Vон	(I _{IO} = +20 mA)	V _{DD} = 3.3 V	2.91	_	_	V
		V _{DD} = 3.6 V	3.23	_	_	
R _{PU} ⁽²⁾	Internal pull-up resistor	_	_	40	_	kΩ
R _{PD} ⁽²⁾	Internal pull-down resistor	_	_	40	_	kΩ

^{(1).} Based on characterization, not tested in production.

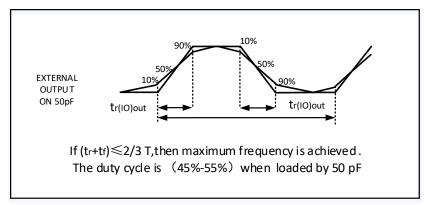
^{(2).} Guaranteed by design, not tested in production.



GPIOx_MDy[1:0] bit value ⁽³⁾	Parameter	Conditions	Max	Unit
		$1.8 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}, C_L = 10 \text{ pF}$	9	
GPIOx_CTL->MDy[1:0] = 10 (IO_Speed = 2 MHz)	frequency ⁽⁴⁾	$1.8 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}, C_L = 30 \text{ pF}$	6	MHz
(10_Speed = 2 Wil 12)	1.	$1.8 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}, C_L = 50 \text{ pF}$	4	
CDIOv CTI > MDv(1:01 - 01	Maximum	$1.8 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}, C_L = 10 \text{ pF}$	50	
GPIOx_CTL->MDy[1:0] = 01 (IO_Speed = 10 MHz)	frequency ⁽⁴⁾	$1.8 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}, C_L = 30 \text{ pF}$	25	MHz
(10_Speed = 10 Wil 12)		1.8 V≤ V _{DD} ≤ 3.6 V, C _L = 50 pF	15	
GPIOx_CTL->MDy[1:0] = 11	Maximum	1.8 V≤ V _{DD} ≤ 3.6 V, C _L = 10 pF	60	
(IO_Speed = 50 MHz)	frequency ⁽⁴⁾	1.8 V≤ V _{DD} ≤ 3.6 V, C _L = 30 pF	30	MHz
(10_5peed = 30 Wil 12)	irequericy.	$1.8 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}, C_L = 50 \text{ pF}$	20	
GPIOx_CTL->MDy[1:0] = 11 and	Maximum	1.8 V≤ V _{DD} ≤ 3.6 V, C _L = 10 pF	70	
GPIOx_SPDy = 1	frequency ⁽⁴⁾	1.8 V≤ V _{DD} ≤ 3.6 V, C _L = 30 pF	50	MHz
(IO_Speed = MAX)	irequericy. 7	1.8 V≤ V _{DD} ≤ 3.6 V, C _L = 50 pF	30	

- (1). Based on characterization, not tested in production.
- (2). Unless otherwise specified, all test results given for TA = 25 $\,\,^{\circ}\!\mathrm{C}\,.$
- (3). The I/O speed is configured using the GPIOx_CTL -> MDy[1:0] bits. Refer to the GD32E103xx user manual which is selected to set the GPIO port output speed.
- (4). The maximum frequency is defined in Figure 4-1.

Figure 4-1. I/O port AC characteristics definition



4.13. ADC characteristics

Table 4-26. ADC characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DDA}^{(1)}$	Operating voltage	_	2.4	3.3	3.6	V
V _{IN} ⁽¹⁾	ADC input voltage range	_	0	_	V_{REF+}	V
f _{ADC} ⁽¹⁾	ADC clock	_	0.1	_	42	MHz
		12-bit	0.007	_	3	
fs ⁽¹⁾	Compling rate	10-bit	0.008	_	3.5	MSP
IS ⁽⁻⁾	Sampling rate	8-bit	0.01	_	4.2	S
		6-bit	0.011	_	5.25	
V _{AIN} ⁽¹⁾	Analog input voltage	16 external; 2 internal	0	_	V _{DDA}	V



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{REF+} ⁽²⁾	Positive Reference Voltage	_	_	V_{DDA}	_	V
V _{REF-} (2)	Negative Reference Voltage	_		0		V
R _{AIN} ⁽²⁾	External input impedance	See Equation 1		-	24	kΩ
R _{ADC} ⁽²⁾	Input sampling switch resistance			l	0.2	kΩ
C _{ADC} ⁽²⁾	Input sampling capacitance	No pin/pad capacitance included			5.5	pF
t _{CAL} (2)	Calibration time	$f_{ADC} = 42 \text{ MHz}$		3.12		μs
t _s (2)	Sampling time	$f_{ADC} = 42 \text{ MHz}$	0.036		5.7	μs
	Total as mysersian	12-bit	_	14	_	
t _{CONV} (2)	Total conversion	10-bit	_	12	_	1/
(CONV'-)	time(including sampling time)	8-bit		10		f_{ADC}
	unie)	6-bit		8		
tsu ⁽²⁾	Startup time				1	μS

^{(1).} Based on characterization, not tested in production.

$$\textit{Equation 1}: \text{R}_{\text{AIN}} \text{ max formula } R_{\text{AIN}} < \frac{T_{\text{S}}}{f_{\text{ADC}}*C_{\text{ADC}}*ln(2^{N+2})} - R_{\text{ADC}}$$

The formula above (Equation 1) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).

Table 4-27. ADC RAIN max for $f_{ADC} = 42 \text{ MHz}$

T _s (cycles)	t _s (us)	R _{AINmax} (kΩ)
1.5	0.04	0.47
7.5	0.18	3.15
13.5	0.32	5.82
28.5	0.68	12.55
41.5	0.99	18.35
55.5	1.32	24.55
71.5	1.70	NA
239.5	5.70	NA

Table 4-28. ADC dynamic accuracy at $f_{ADC} = 14 \text{ MHz}^{(1)}$

Symbol	Parameter	Test conditions	Min	Тур	Max	Unit
ENOB	Effective number of bits	$f_{ADC} = 14 \text{ MHz}$	_	10.3		bits
SNDR	Signal-to-noise and distortion ratio	$V_{DDA} = V_{REF+} = 3.3 \text{ V}$	_	63.8	_	
SNR	Signal-to-noise ratio	Input Frequency = 20	_	64.5	_	dB
THD	Total harmonic distortion	KHz		-67.5		uв
1110	Total Halfflorile distortion	Temperature = 25 °C		-07.3		

^{(1).} Based on characterization, not tested in production.

^{(2).} Guaranteed by design, not tested in production.



Table 4-29. ADC dynamic accuracy at f_{ADC} = 42 MHz⁽¹⁾

Symbol	Parameter	Test conditions	Min	Тур	Max	Unit
ENOB	Effective number of bits	f _{ADC} = 42 MHz	_	10.3	_	bits
SNDR	Signal-to-noise and distortion ratio	$V_{DDA} = V_{REF+} = 3.3 \text{ V}$	_	63.8	_	
SNR	Signal-to-noise ratio	Input Frequency = 20 KHz	_	64.5	_	dB
THD	Total harmonic distortion	Temperature = 25 °C	_	-67.5	_	

^{(1).} Based on characterization, not tested in production.

Table 4-30. ADC static accuracy at f_{ADC} = 42 MHz⁽¹⁾

Symbol	Parameter	Test conditions	Тур	Max	Unit
Offset	Offset error	f 42 MH=	±1	_	
DNL	Differential linearity error	f _{ADC} = 42 MHz	±1	_	LSB
INL	Integral linearity error	$V_{DDA} = V_{REF+} = 3.3 \text{ V}$	±3		

^{(1).} Based on characterization, not tested in production.

4.14. Temperature sensor characteristics

Table 4-31. Temperature sensor characteristics(1)

Symbol	Parameter	Min	Тур	Max	Unit
TL	VSENSE linearity with temperature	_	±1.5	_	$^{\circ}$
Avg_Slope	Average slope	_	4.3	_	mV/°C
V ₂₅	Voltage at 25 °C	_	1.47	_	V
tstart	Startup time	_	_	_	μs
ts_temp ⁽²⁾	ADC sampling time when reading the temperature	_	17.1	_	μs

^{(1).} Based on characterization, not tested in production.

4.15. DAC characteristics

Table 4-32. DAC characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DDA}^{(1)}$	Operating voltage	_	1.71	3.3	3.6	V
V _{REF+} ⁽¹⁾	Reference supply voltage	V _{REF+} should always below V _{DDA}	1.71	_	3.6	V
R _{LOAD} ⁽²⁾	Load resistance	Resistive load with buffer ON		_	_	kΩ
Ro ⁽²⁾	Impedance output with buffer OFF	_			15	kΩ
C _{LOAD} ⁽²⁾	Load capacitance	No pin/pad capacitance included	_	_	50	pF
DAC_OUT min ⁽²⁾	Lower DAC_OUT voltage with buffer ON	_	0.2		_	V

^{(2).} Shortest sampling time can be determined in the application by multiple iterations.



Symbol	Parameter	Conditions	Min	Тур	Max	Unit				
DAC_OUT	Higher DAC_OUT voltage				V _{DDA} -	V				
max ⁽²⁾	with buffer ON	_	_	_	0.2	V				
DAC_OUT	Lower DAC_OUT voltage			0.5		mV				
min ⁽²⁾	with buffer OFF	_	_	0.5	_	IIIV				
DAC_OUT	Higher DAC_OUT voltage				V _{DDA} -	V				
max ⁽²⁾	with buffer OFF				1LSB	V				
		With no load, middle								
		code(0x800) on the input, V _{REF+}	_	380	_	μΑ				
I _{DDA} ⁽¹⁾	DAC current consumption	= 3.6 V								
IDDA	in quiescent mode	With no load, worst								
		code(0xF1C) on the input, V _{REF+}	_	460	_	μΑ				
		= 3.6 V								
		With no load, middle								
		code(0x800) on the input, V _{REF+}	_	120	_	μΑ				
I _{DDVREF+} (1)	DAC current consumption	= 3.6 V With no load, worst								
IDDVREF+\''	in quiescent mode									
		code(0xF1C) on the input, V _{REF+}	_	320	_	μΑ				
		= 3.6 V								
DNL ⁽¹⁾	Differential non-linearity	DAC in 12-bit mode			±3	LSB				
DINL	error	DAC III 12-bit IIIode		DAC III 12-bit IIIode		DAC III 12-bit mode			ე -	LOD
INL ⁽¹⁾	Integral non-linearity	DAC in 12-bit mode	_	1	±4	LSB				
Offset ⁽¹⁾	Offset error	DAC in 12-bit mode	_		±12	LSB				
GE ⁽¹⁾	Gain error	DAC in 12-bit mode	_		±0.5	%				
T _{setting} (1)	Settling time	C_{LOAD} ≤50 pF, R_{LOAD} ≥5 kΩ	_	0.3	1	μs				
Update	Max frequency for a correct									
rate ⁽²⁾	DAC_OUT change from	C _{LOAD} ≤50 pF, R _{LOAD} ≥5 kΩ	_	_	4	MS/s				
rate	code i to i±1LSBs									
	Power supply rejection									
PSRR ⁽²⁾	ratio	_	55	80	_	dB				
	(to V _{DDA})									

^{(1).} Based on characterization, not tested in production.

4.16. I2C characteristics

Table 4-33. I2C characteristics(1)(2)

Symbol	Parameter	Conditions	Standard mode Fas		Fast r	node	Fast i	mode us	Unit
			Min	Max	Min	Max	Min	Max	
t _{SCL(H)}	SCL clock high time	_	4.0		0.6	_	0.2	_	μs
t _{SCL(L)}	SCL clock low time	_	4.7		1.3	_	0.5	_	μs
t _{su(SDA)}	SDA setup time	_	2		0.8		0.1	_	μs

^{(2).} Guaranteed by design, not tested in production.

t _{h(SDA)}	SDA data hold time	_	250		250		130		ns
$t_{r(\text{SDA/SCL})}$	SDA and SCL rise time			1000	20	300		120	ns
t _{f(SDA/SCL)}	SDA and SCL fall time	_	4	300	4	300	4	120	ns
t _{h(STA)}	Start condition hold time	1	4.0		0.6		0.26		μs

^{(1).} Guaranteed by design, not tested in production

4.17. SPI characteristics

Table 4-34. Standard SPI characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
fsck	SCK clock frequency	_	_	_	30	MHz
t _{SCK(H)}	SCK clock high time	Master mode, f _{PCLKx} = 120 MHz, presc = 8	31.83	33.33	34.83	ns
tsck(L)	SCK clock low time	Master mode, f _{PCLKx} = 120 MHz, presc = 8	31.83	33.33	34.83	ns
		SPI master mode				
t _{V(MO)}	Data output valid time	_	_	7		ns
t _{H(MO)}	Data output hold time	_	_	4		ns
tsu(MI)	Data input setup time	_	1	_		ns
t _{H(MI)}	Data input hold time	_	0	_		ns
		SPI slave mode				
t _{SU(NSS)}	NSS enable setup time	_	0	_		ns
t _{H(NSS)}	NSS enable hold time	_	1	_		ns
t _{A(SO)}	Data output access time	_	_	9		ns
t _{DIS(SO)}	Data output disable time	_	_	8		ns
t _{V(SO)}	Data output valid time	_	_	10		ns
t _{H(SO)}	Data output hold time	_		10	_	ns
tsu(si)	Data input setup time	_	0		_	ns
t _{H(SI)}	Data input hold time	_	2	_	_	ns

^{(1).} Based on characterization, not tested in production.

4.18. I2S characteristics

Table 4-35. I2S characteristics(1)(2)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
fск		Master mode (data: 16 bits, Audio frequency = 96 kHz)	ı	3.078		MHz
		Slave mode	_	10		
t _H	Clock high time	_		162		ns

^{(2).} Test condition: GPIO_SPEED set 2MHz and external pull-up resistor value is 1 k Ω when operate EEPROM with I2C



t∟	Clock low time		_	163	_	ns
t _{V(WS)}	WS valid time	Master mode	_	2	_	ns
t _{H(WS)}	WS hold time	Master mode	_	2	_	ns
tsu(ws)	WS setup time	Slave mode	0	_	_	ns
t _{H(WS)}	WS hold time	Slave mode	3	_	_	ns
DuCy _(SCK)	I2S slave input clock duty cycle	Slave mode	_	50	_	%
tsu(sd_mr)	Data input setup time	Master mode	0	_	_	ns
t _{su(SD_SR)}	Data input setup time	Slave mode	0	_	_	ns
t _{H(SD_MR)}	Data input hold time	Master receiver	1	_	_	ns
t _{H(SD_SR)}	Data input hold time	Slave receiver	3	_	_	ns
t _{v(SD_ST)}	Data output valid time	Slave transmitter (after enable edge)	_	12		ns
th(SD_ST)	Data output hold time	Slave transmitter (after enable edge)	_	10	_	ns
t _{v(SD_MT)}	Data output valid time	Master transmitter (after enable edge)	_	10	_	ns
th(SD_MT)	Data output hold time	Master transmitter (after enable edge)	_	7	_	ns

^{(1).} Guaranteed by design, not tested in production.

4.19. USART characteristics

Table 4-36. USART characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{SCK}	SCK clock frequency	f _{PCLKx} = 120 MHz		_	60	MHz
t _{SCK(H)}	SCK clock high time	f _{PCLKx} = 120 MHz	7.5	_	_	ns
tsck(L)	SCK clock low time	f _{PCLKx} = 120 MHz	7.5	_	_	ns

^{(1).} Guaranteed by design, not tested in production.

4.20. CAN characteristics

Refer to <u>Table 4-24. I/O port DC characteristics</u> for more details on the input/output alternate function characteristics (CANTX and CANRX).

4.21. USBFS characteristics

Table 4-37. USBFS start up time

Symbol	Parameter	Max	Unit
tstartup ⁽¹⁾	USBFS startup time	1	μs

^{(1).} Guaranteed by design, not tested in production.

^{(2).} Based on characterization, not tested in production.



Table 4-38. USBFS DC electrical characteristics

Symb	ol	Parameter	Conditions	Min	Тур	Max	Unit
	V_{DD}	USBFS operating voltage		3	_	3.6	V
	V_{DI}	Differential input sensitivity		0.2	_		
Input	Vсм	Differential common mode	Includes V _{DI} range	0.8		2.5	
levels ⁽¹⁾	V CIVI	range	includes vol range	0.0	_	2.5	V
	V _{SE}	Single ended receiver	_	1.3	_	2.0	
		threshold	_	1.5		2.0	
Output	Vol	Static output level low	R∟of 1.0K to 3.6 V	_	0.064	0.3	V
Levels ⁽²⁾	Vон	Static output level high	R_L of 15K to V_{SS}	2.8	3.3	3.6	V
R _{PD} ⁽²	2)	PA11, PA12(USB_DM/DP)	$V_{IN} = V_{DD}$	17	20.574	24	
LYPD,	,	PA9(USB_VBUS)	VIN = VDD	0.65	_	2.0	kΩ
R _{PU} ⁽²	2)	PA11, PA12(USB_DM/DP)	VIN = Vss	1.5	1.585	2.1	V77
K50/-	,	PA9(USB_VBUS)	VIN = VSS	0.25	0.326	0.55	

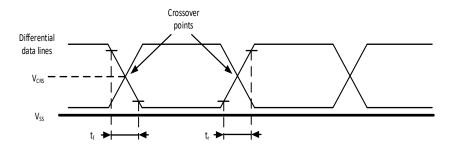
^{(1).} Guaranteed by design, not tested in production.

Table 4-39. USBFS electrical characteristics(1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _R	Rise time	$C_L = 50 pF$	4	_	20	ns
t _F	Fall time	$C_L = 50 pF$	4	_	20	ns
t _{RFM}	Rise/ fall time matching	t _R /t _F	90	_	110	%
Vcrs	Output signal crossover voltage	_	1.3	_	2.0	V

^{(1).} Guaranteed by design, not tested in production.

Figure 4-2. USBFS timings: definition of data signal rise and fall time



4.22. EXMC characteristics

Table 4-40. Asynchronous non-multiplexed SRAM/PSRAM/NOR read timings(1)(2)(3)(4)

Symbol	Parameter	Min	Max	Unit
t _{w(NE)}	t _{w(NE)} EXMC_NE low time		42.5	ns
tv(noe_ne)	EXMC_NEx low to EXMC_NOE low	0	_	ns
t _{w(NOE)}	EXMC_NOE low time	40.5	42.5	ns
th(NE_NOE)	EXMC_NOE high to EXMC_NE high hold time	0	_	ns
t _{v(A_NE)}	EXMC_NEx low to EXMC_A valid	0	_	ns

^{(2).} Based on characterization, not tested in production.



t _{v(BL_NE)}	EXMC_NEx low to EXMC_BL valid	0	_	ns
t _{su(DATA_NE)}	Data to EXMC_NEx high setup time	32.2	_	ns
t _{su(DATA_NOE)}	Data to EXMC_NOEx high setup time	32.2	_	ns
th(DATA_NOE)	Data hold time after EXMC_NOE high	0	_	ns
th(DATA_NE)	Data hold time after EXMC_NEx high	0	_	ns
t _{v(NADV_NE)}	EXMC_NEx low to EXMC_NADV low	0	ı	ns
t _{w(NADV)}	EXMC_NADV low time	7.3	9.3	ns

- (1). C_L=30 pF.
- (2). Guaranteed by design, not tested in production.
- (3). Based on characterization, not tested in production.
- (4). Based on configure: f_{HCLK}=120 MHz, AddressSetupTime=0, AddressHoldTime=1, DataSetupTime =1.

Table 4-41. Asynchronous non-multiplexed SRAM/PSRAM/NOR write timings(1)(2)(3)(4)

	•			
Symbol	Parameter	Min	Max	Unit
t _{w(NE)}	EXMC_NE low time	23.9	25.9	ns
tv(NWE_NE)	EXMC_NEx low to EXMC_NWE low	7.3	_	ns
t _{w(NWE)}	EXMC_NWE low time	7.3	9.3	ns
t _{h(NE_NWE)}	EXMC_NWE high to EXMC_NE high hold time	7.3	9.3	ns
t _{v(A_NE)}	EXMC_NEx low to EXMC_A valid	0	_	ns
tv(nadv_ne)	EXMC_NEx low to EXMC_NADV low	0	_	ns
t _{w(NADV)}	EXMC_NADV low time	7.3	9.3	ns
t _{h(AD_NADV)}	EXMC_AD(address) valid hold time after EXMC_NADV high	15.6	_	ns
t _{h(A_NWE)}	Address hold time after EXMC_NWE high	7.3	_	ns
t _{h(BL_NWE)}	EXMC_BL hold time after EXMC_NWE high	7.3	_	ns
t _{v(BL_NE)}	EXMC_NEx low to EXMC_BL valid	0	_	ns
t _{v(DATA_NADV)}	EXMC_NADV high to DATA valid	0	_	ns
t _{h(DATA_NWE)}	Data hold time after EXMC_NWE high	7.3	_	ns

- (1). $C_L=30 pF$.
- (2). Guaranteed by design, not tested in production.
- (3). Based on characterization, not tested in production.
- (4). Based on configure : $f_{HCLK} = 120 MHz$, Address Setup Time = 0, Address Hold Time = 1, Data Setup Time = 1.

Table 4-42. Asynchronous multiplexed PSRAM/NOR read timings(1)(2)(3)(4)

Symbol	Parameter	Min	Max	Unit
t _{w(NE)}	EXMC_NE low time	57.1	59.1	ns
tv(noe_ne)	EXMC_NEx low to EXMC_NOE low	23.9	_	ns
tw(NOE)	EXMC_NOE low time	32.2	34.2	ns
th(NE_NOE)	EXMC_NOE high to EXMC_NE high hold time	0	_	ns
t _{v(A_NE)}	EXMC_NEx low to EXMC_A valid	0	_	ns
t _{v(A_NOE)}	Address hold time after EXMC_NOE high	0	_	ns
t _{v(BL_NE)}	EXMC_NEx low to EXMC_BL valid	0	_	ns
th(BL_NOE)	th(BL_NOE) EXMC_BL hold time after EXMC_NOE high		_	ns
t _{su(DATA_NE)}	Data to EXMC_NEx high setup time	33.2	_	ns



t _{su(DATA_NOE)}	Data to EXMC_NOEx high setup time	_	ns	
th(DATA_NOE)	Data hold time after EXMC_NOE high	0	_	ns
t _{h(DATA_NE)}	Data hold time after EXMC_NEx high	0	_	ns
t _{v(NADV_NE)}	EXMC_NEx low to EXMC_NADV low	0	_	ns
t _{w(NADV)}	EXMC_NADV low time	7.3	9.3	ns
T _{h(AD_NADV)}	EXMC_AD(adress) valid hold time after	7.3	9.3	ns
	EXMC_NADV high	1.3	স. ১	

- (1). C_L=30 pF.
- (2). Guaranteed by design, not tested in production.
- (3). Based on characterization, not tested in production.
- $(4). \ Based \ on \ configure: f_{HCLK} = 120MHz, AddressSetupTime = 0, \ AddressHoldTime = 1, \ DataSetupTime = 1; \\$

Table 4-43. Asynchronous multiplexed PSRAM/NOR write timings(1)(2)(3)(4)

Symbol	Parameter	Min	Max	Unit
t _{w(NE)}	EXMC_NE low time	40.5	42.5	ns
tv(NWE_NE)	EXMC_NEx low to EXMC_NWE low	7.3	_	ns
t _{w(NWE)}	EXMC_NWE low time	23.9	25.9	ns
t _{h(NE_NWE)}	EXMC_NWE high to EXMC_NE high hold time	7.3	_	ns
t _{v(A_NE)}	EXMC_NEx low to EXMC_A valid	0	_	ns
tv(nadv_ne)	EXMC_NEx low to EXMC_NADV low	0	_	ns
t _{w(NADV)}	EXMC_NADV low time	7.3	9.3	ns
t _{h(AD_NADV)}	EXMC_AD(address) valid hold time after EXMC_NADV high	7.3	_	ns
t _{h(A_NWE)}	Address hold time after EXMC_NWE high	7.3	_	ns
t _{h(BL_NWE)}	EXMC_BL hold time after EXMC_NWE high	7.3	_	ns
t _{v(BL_NE)}	EXMC_NEx low to EXMC_BL valid	0	_	ns
tv(data_nadv)	EXMC_NADV high to DATA valid	7.3	_	ns
th(DATA_NWE)	Data hold time after EXMC_NWE high	7.3	_	ns

- (1). $C_L=30$ pF.
- (2). Guaranteed by design, not tested in production.
- (3). Based on characterization, not tested in production.
- (4). Based on configure: $f_{HCLK} = 120MHz$, AddressSetupTime = 0, AddressHoldTime = 1, DataSetupTime = 1;

Table 4-44. Synchronous multiplexed PSRAM/NOR read timings(1)(2)(3)(4)

Symbol	Parameter	Min	Max	Unit
tw(CLK)	EXMC_CLK period	33.2	_	ns
td(CLKL-NExL)	EXMC_CLK low to EXMC_NEx low	0	_	ns
t _{d(CLKH-NExH)}	EXMC_CLK high to EXMC_NEx high	15.6	_	ns
td(CLKL-NADVL)	EXMC_CLK low to EXMC_NADV low	0	_	ns
td(CLKL-NADVH)	EXMC_CLK low to EXMC_NADV high	0	_	ns
td(CLKL-AV)	EXMC_CLK low to EXMC_Ax valid	0	_	ns
t _{d(CLKH-AIV)}	EXMC_CLK high to EXMC_Ax invalid	15.6	_	ns
t _{d(CLKL-NOEL)}	EXMC_CLK low to EXMC_NOE low	0	_	ns
t _{d(CLKH-NOEH)}	EXMC_CLK high to EXMC_NOE high	15.6		ns

t _{d(CLKL-ADV)}	EXMC_CLK low to EXMC_AD valid	0	ı	ns
td(CLKL-ADIV)	EXMC_CLK low to EXMC_AD invalid	0	_	ns

- (1). $C_L=30$ pF.
- (2). Guaranteed by design, not tested in production.
- (3). Based on characterization, not tested in production.
- (4). Based on configure: f_{HCLK} =120 MHz, BurstAccessMode = Enable; MemoryType = PSRAM; WriteBurst = Enable; CLKDivision = 3(EXMC_CLK is 4 divided by f_{HCLK}); DataLatency = 1.

Table 4-45. Synchronous multiplexed PSRAM write timings(1)(2)(3)(4)

Symbol	Parameter	Min	Max	Unit
t _{w(CLK)}	EXMC_CLK period	33.2	1	ns
t _{d(CLKL-NExL)}	EXMC_CLK low to EXMC_NEx low	0	_	ns
t _{d(CLKH-NExH)}	EXMC_CLK high to EXMC_NEx high	15.6	_	ns
td(CLKL-NADVL)	EXMC_CLK low to EXMC_NADV low	0	_	ns
td(CLKL-NADVH)	EXMC_CLK low to EXMC_NADV high	0	_	ns
td(CLKL-AV)	EXMC_CLK low to EXMC_Ax valid	0	_	ns
t _{d(CLKH-AIV)}	EXMC_CLK high to EXMC_Ax invalid	15.6	_	ns
td(CLKL-NWEL)	EXMC_CLK low to EXMC_NWE low	0	_	ns
t _d (CLKH-NWEH)	EXMC_CLK high to EXMC_NWE high	15.6	_	ns
td(CLKL-ADIV)	EXMC_CLK low to EXMC_AD invalid	0		ns
t _d (CLKL-DATA)	EXMC_A/D valid data after EXMC_CLK low	0	_	ns
th(CLKL-NBLH)	EXMC_CLK low to EXMC_NBL high	C_CLK low to EXMC_NBL high 0 —		ns

- (1). C_L=30 pF.
- (2). Guaranteed by design, not tested in production.
- (3). Based on characterization, not tested in production.
- (4). Based on configure: f_{HCLK} =120 MHz, BurstAccessMode = Enable; MemoryType = PSRAM; WriteBurst = Enable; CLKDivision = 3(EXMC_CLK is 4 divided by f_{HCLK}); DataLatency = 1.

Table 4-46. Synchronous non-multiplexed PSRAM/NOR read timings(1)(2)(3)(4)

Symbol	Parameter	Min	Max	Unit
tw(CLK)	EXMC_CLK period	33.2		ns
t _{d(CLKL-NExL)}	EXMC_CLK low to EXMC_NEx low	0		ns
t _{d(CLKH-NExH)}	EXMC_CLK high to EXMC_NEx high	15.6		ns
td(CLKL-NADVL)	EXMC_CLK low to EXMC_NADV low	0		ns
t _{d(CLKL-NADVH)}	EXMC_CLK low to EXMC_NADV high	0		ns
td(CLKL-AV)	EXMC_CLK low to EXMC_Ax valid	0		ns
t _{d(CLKH-AIV)}	EXMC_CLK high to EXMC_Ax invalid	15.6		ns
t _{d(CLKL-NOEL)}	EXMC_CLK low to EXMC_NOE low	0	_	ns
t _d (CLKH-NOEH)	EXMC_CLK high to EXMC_NOE high	15.6	_	ns

- (1). $C_L=30 pF$.
- (2). Guaranteed by design, not tested in production.
- (3). Based on characterization, not tested in production.
- (4). Based on configure: f_{HCLK} =120 MHz, BurstAccessMode = Enable; MemoryType = PSRAM; WriteBurst = Enable; CLKDivision = 3(EXMC_CLK is 4 divided by f_{HCLK}); DataLatency = 1.



Table 4-47. Synchronous non-multiplexed PSRAM write timings(1)(2)(3)(4)

Symbol	Parameter	Min	Max	Unit
tw(CLK)	EXMC_CLK period	33.2	_	ns
t _{d(CLKL-NExL)}	EXMC_CLK low to EXMC_NEx low	0	_	ns
t _{d(CLKH-NExH)}	EXMC_CLK high to EXMC_NEx high	15.6		ns
td(CLKL-NADVL)	EXMC_CLK low to EXMC_NADV low	0		ns
td(CLKL-NADVH)	EXMC_CLK low to EXMC_NADV high	0	_	ns
t _{d(CLKL-AV)}	EXMC_CLK low to EXMC_Ax valid	0	_	ns
t _{d(CLKH-AIV)}	EXMC_CLK high to EXMC_Ax invalid	15.6		ns
t _{d(CLKL-NWEL)}	EXMC_CLK low to EXMC_NWE low	0	_	ns
td(CLKH-NWEH)	EXMC_CLK high to EXMC_NWE high	15.6	_	ns
td(CLKL-DATA)	EXMC_A/D valid data after EXMC_CLK low 0 —			ns
th(CLKL-NBLH)	EXMC_CLK low to EXMC_NBL high	0	_	ns

^{(1).} $C_L=30 pF$.

4.23. TIMER characteristics

Table 4-48. TIMER characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
+	Timer resolution time	_	1	ı	tTIMERXCLK
t _{res}	Timer resolution time	f _{TIMERxCLK} = 120 MHz	8.4	_	ns
fехт	Timer external clock	_	0	ftimerxclk/2	MHz
IEXI	frequency	ftimerxclk = 120 MHz	0	60	MHz
RES	Timer resolution	_	_	16	bit
	16-bit counter clock period	_	1	65536	t _{TIMERxCLK}
tcounter	when internal clock is selected	f _{TIMERxCLK} = 120 MHz	0.0084	546	μs
they count	Maximum possible count	_	_	65536x65536	tTIMERXCLK
tmax_count	iviaximum possible count	f _{TIMERxCLK} = 120 MHz	_	35.7	s

 $[\]hbox{ (1). Guaranteed by design, not tested in production.} \\$

4.24. WDGT characteristics

^{(2).} Guaranteed by design, not tested in production.

^{(3).} Based on characterization, not tested in production.

^{(4).} Based on configure: $f_{HCLK} = 120$ MHz, BurstAccessMode = Enable; MemoryType = PSRAM; WriteBurst = Enable; CLKDivision = $3(EXMC_CLK$ is 4 divided by f_{HCLK}); DataLatency = 1.



Table 4-49. FWDGT min/max timeout period at 40 kHz (IRC40K) (1)

Prescaler divider	PR[2:0] bits	Min timeout RLD[11:0] = 0x000	Max timeout RLD[11:0] = 0xFFF	Unit
1/4	000	0.1	409.6	
1/8	001	0.2	819.2	
1/16	010	0.4	1638.4	
1/32	011	0.8	3276.8	ms
1/64	100	1.6	6553.6	
1/128	101	3.2	13107.2	
1/256	110 or 111	6.4	26214.4	

^{(1).} Guaranteed by design, not tested in production.

Table 4-50. WWDGT min-max timeout value at 60 MHz (f_{PCLK1}) ⁽¹⁾

Prescaler divider	PSC[2:0]	Min timeout value CNT[6:0] = 0x40	Unit	Max timeout value CNT[6:0] = 0x7F	Unit
1/1	00	68.27		4.37	
1/2	01	136.53		8.74	
1/4	10	273.07	μs	17.48	ms
1/8	11	546.13		34.96	

^{(1).} Guaranteed by design, not tested in production.

4.25. Parameter conditions

1. Unless otherwise specified, all values given for $V_{DD} = V_{DDA} = 3.3 \text{ V}$, $T_A = 25 \, ^{\circ}\text{C}$.



5. Package information

5.1. QFN package outline dimensions

Figure 5-1. QFN package outline

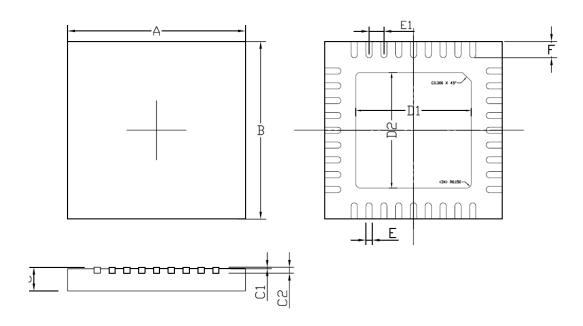


Table 5-1. QFN package dimensions

Cumbal	Dimensions (mm)		Cumbal	Dimension	ns (mm)
Symbol	min	max	Symbol	min	max
Α	6.0 ±	0.1	D1	3.90	Тур
В	6.0 ±	6.0 ± 0.1		3.90 Typ	
С	0.85	0.95	E	0.210 ± 0.025	
C1	0~0.050		E1	0.500 Typ	
C2	0.203 Typ		F	0.550	Тур

(Original dimensions are in millimeters)

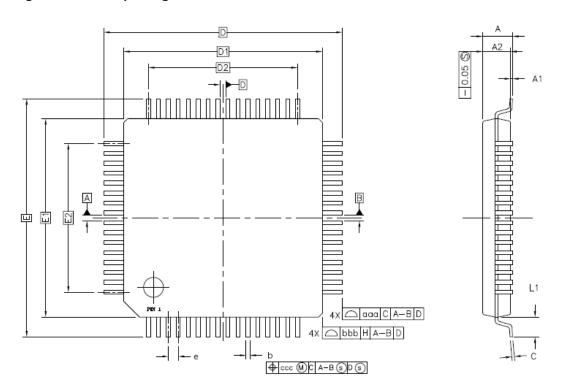
Notes:

- 1. Formed lead shall be planar with respect to one another within 0.004 inches.
- 2. Both package length and width do not include mold flash and metal burr.



5.2. LQFP package outline dimensions

Figure 5-2. LQFP package outline



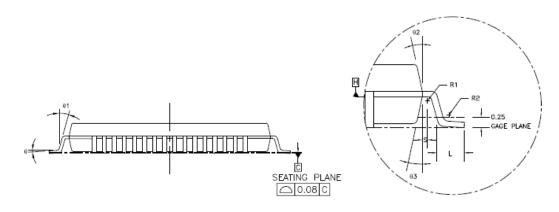


Table 5-2. LQFP package dimensions

Cumah al		LQFP48		LQFP64			LQFP100		
Symbol	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max
А	1.20	ı	1.50	-	ı	1.60	ı	ı	1.60
A1	0.05	-	0.15	0.05	-	0.15	0.05	-	0.15
A2	0.95	1.00	1.35	1.35	1.40	1.45	1.35	1.40	1.45
D	8.80	9.00	9.20	11.80	12.00	12.20	15.80	16.00	16.20
D1	6.90	7.00	7.10	9.90	10.00	10.10	13.90	14.00	14.10
Е	8.80	9.00	9.20	11.80	12.00	12.20	15.80	16.00	16.20
E1	6.90	7.00	7.10	9.90	10.00	10.10	13.90	14.00	14.10



Ob l	LQFP48			LQFP64			LQFP100		
Symbol	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max
R1	0.08	-	-	0.08	-	-	0.08	-	-
R2	0.08	-	0.20	0.08	-	0.20	0.08	-	0.20
θ	0°	3.5°	7°	0°	3.5°	7°	0°	3.5°	7°
θ1	0°	-	-	0°	-	-	0°	-	-
θ2	11°	12°	13°	11°	12°	13°	11°	12°	13°
θ3	11°	12°	13°	11°	12°	13°	11°	12°	13°
С	0.09	-	0.20	0.09	-	0.20	0.09	-	0.20
L	0.45	0.60	0.75	0.45	0.60	0.75	0.45	0.60	0.75
L1	-	1.00	-	-	1.00	-	-	1.00	-
S	0.20	-	-	0.20	-	-	0.20	-	-
b	0.17	0.22	0.27	0.17	0.20	0.27	0.17	0.20	0.27
е	-	0.50	-	-	0.50	-	-	0.50	-
D2	-	5.50	-	-	7.50	-	-	12.00	-
E2	-	5.50	-	-	7.50	-	-	12.00	-
aaa		0.20			0.20			0.20	
bbb	0.20		0.20		0.20				
ccc	0.08		0.08		0.08				

(Original dimensions are in millimeters)



6. Ordering information

Table 6-1. Part ordering code for GD32E103xx devices

Ordering code Flash (KB)		Package	Package type	Temperature operating range	
GD32E103T8U6	64	QFN36	Green	Industrial -40°C to +85°C	
GD32E103TBU6	128	QFN36	Green	Industrial -40°C to +85°C	
GD32E103C8T6	64	LQFP48	Green	Industrial -40°C to +85°C	
GD32E103CBT6	128	LQFP48	Green	Industrial -40°C to +85°C	
GD32E103R8T6	64	LQFP64	Green	Industrial -40°C to +85°C	
GD32E103RBT6	128	LQFP64	Green	Industrial -40°C to +85°C	
GD32E103V8T6 64		LQFP100	Green	Industrial -40°C to +85°C	
GD32E103VBT6	128	LQFP100	Green	Industrial -40°C to +85°C	



7. Revision history

Table 7-1. Revision history

Revision No.	Description	Date	
1.0	Initial Release	Dec. 26, 2017	
1.1	Modify section <u>2.6</u> Pin definitions	Oct. 29, 2018	
1.2	Repair history accumulation error	Dec. 12, 2018	
1.3	Modify section <u>5.2</u> LQFP package outline dimensions	Apr. 22, 2019	
1.4	Modify section <u>2.6</u> Pin definitions	Jun. 26, 2019	



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